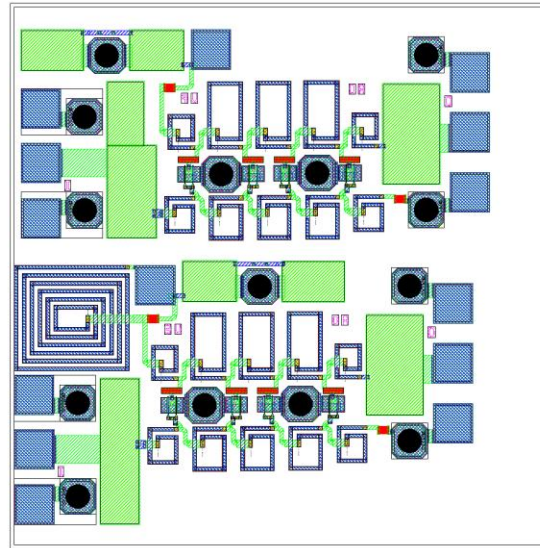


JHU Fall 12 MMIC Design

Measured Results

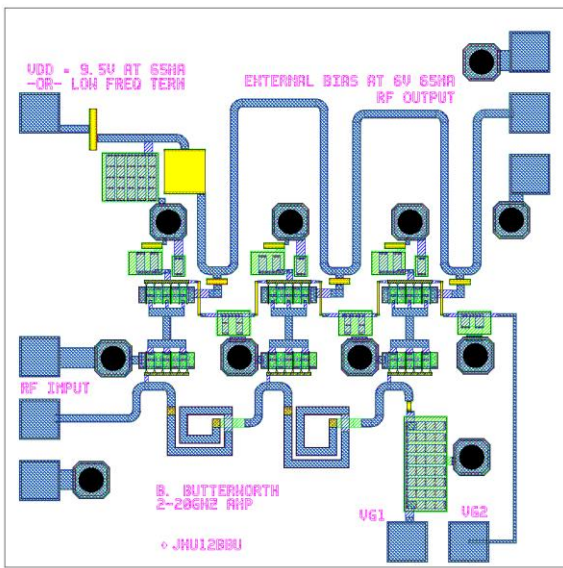
2011/2012 Distributed Amplifiers JEP



Many of the 2012 student designs were broadband distributed amplifiers, with a couple of voltage controlled oscillator designs (VCO), broadband low noise amplifiers, and a balanced amplifier. Most worked very well. Attached are s-parameter plots, noise figure measurements, etc. summarizing the testing of the Fall 2012 MMIC Design Class. Some additional measurements of circuits filling out the rest of the quarter tile include frequency doublers, distributed amplifiers, VCOs, and other amplifiers.

2012 TQP13 Tile





Brandon Butterworth Distributed Amp

Very broadband high gain (~15 dB), from DC to 22 GHz. Had to be careful biasing the cascode PHEMT stages after inadvertently burning out the first die. Very Good noise fig. (<2 dB) 6-14 GHz.

BBUV4 4V 12 mA $v_{g2}=2.0v$

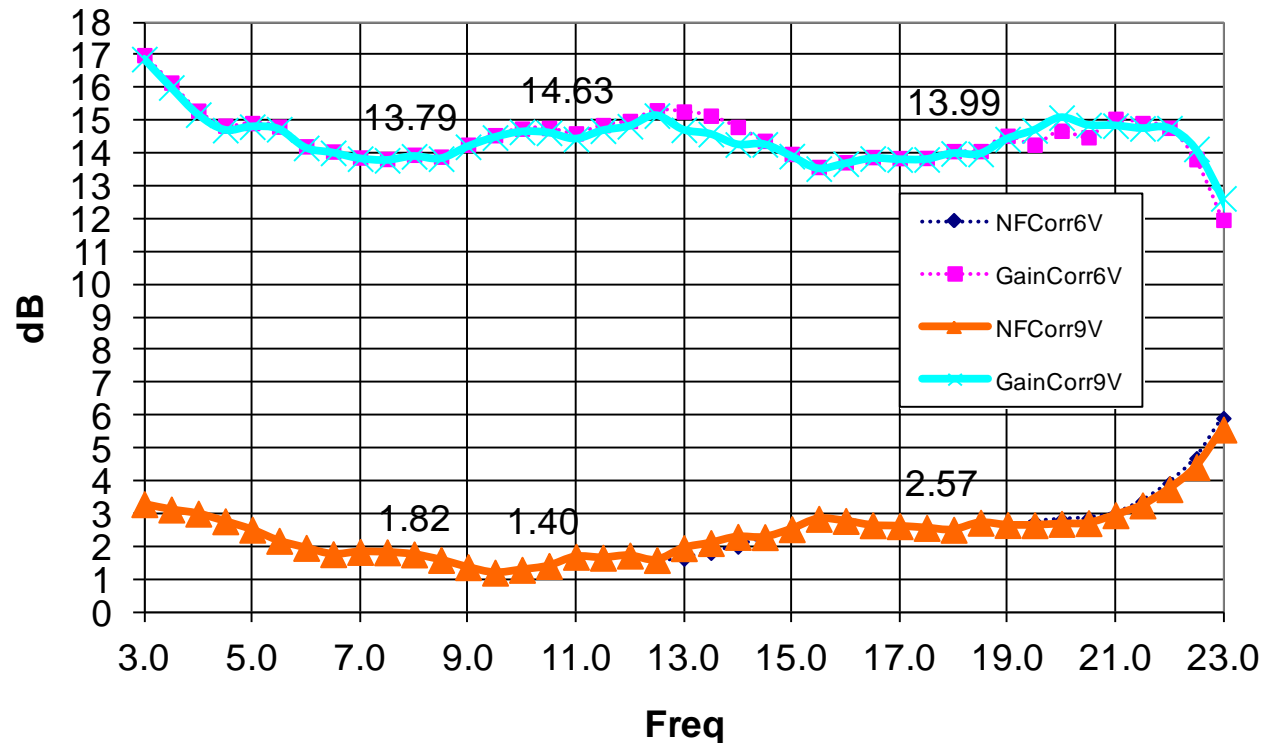
BBUV5 5V 15 mA $v_{g2}=2.5v$

BBUV6 6V 17 mA $v_{g2}=3.0v$

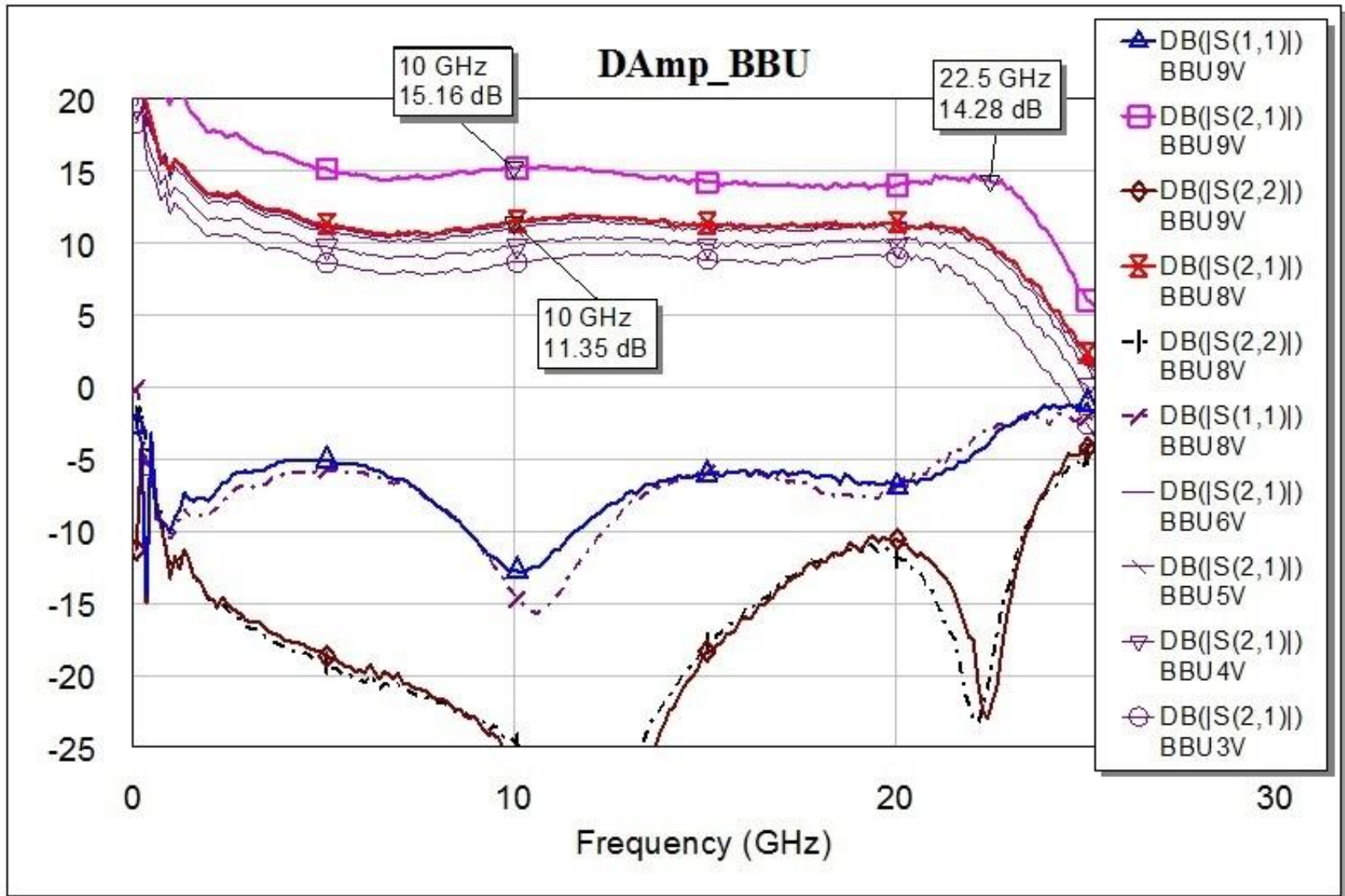
BBUV8 8V 19 mA $v_{g2}=3.0v$

BBUV9 9V 56 mA $v_{g2}=3.0v$ (Best Gain!)

BBU 6, 9V 40ma



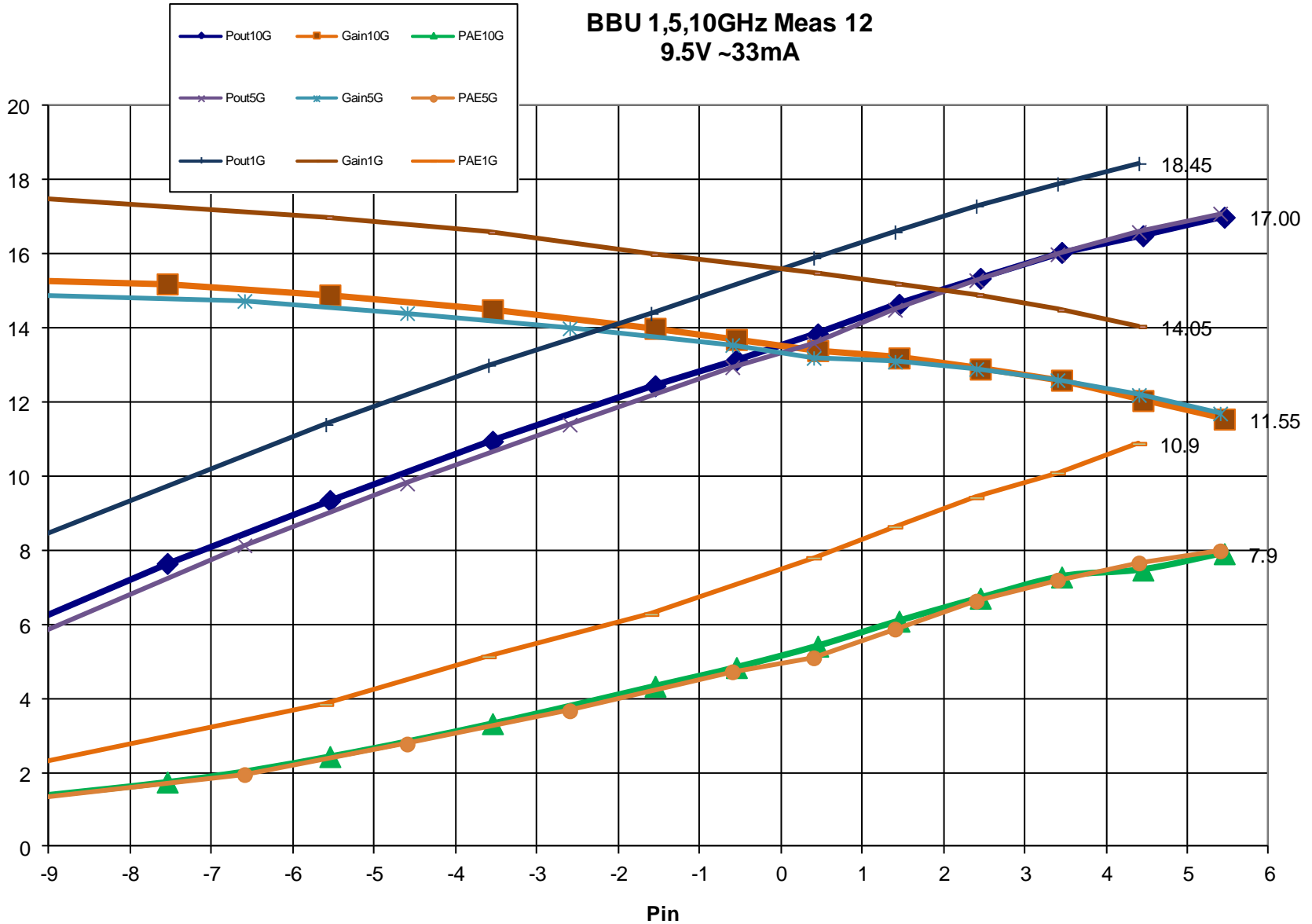
Brandon Butterworth Distributed Amp



Brandon Butterworth Distributed Amp

Performance at 1, 5, 10 GHz AB Bias 9.5V at 33 mA, $v_{g1}=0v$, $v_{g2}=3v$

BBU 1,5,10GHz Meas 12
9.5V ~33mA



Brandon Butterworth Distributed Amp

DC-25 GHz Fall12 TQP13					9.5V ; 33 mA			
Pin(corr)	Pout(corr)	Gain	I1(9.5V)	PDC(mw)	Pout(mw)	Drn Eff	PAE	
-10.60	7.10	17.70	33	313.5	5.13	1.6	1.6	
-5.60	11.40	17.00	37	351.5	13.80	3.9	3.8	
-3.60	13.00	16.60	40	380.0	19.95	5.3	5.1	
-1.60	14.40	16.00	45	427.5	27.54	6.4	6.3	
0.40	15.90	15.50	51	484.5	38.90	8.0	7.8	
1.40	16.60	15.20	54	513.0	45.71	8.9	8.6	
2.40	17.30	14.90	58	551.0	53.70	9.7	9.4	
3.40	17.90	14.50	62	589.0	61.66	10.5	10.1	
4.40	18.45	14.05	65	617.5	69.98	11.3	10.9	

Performance at 1, 5, 10 GHz
 AB Bias 9.5V at 33 mA,
 vg1=0v, vg2=3v

5 GHz		1-5 GHz Fall12 TQP13				4V ; 53 mA				
Die#1	Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(9.5V)	PDC(mw)	Pout(mw)	Drn Eff	PAE
-20.0	-8.10	-21.60	-6.50	15.10		32	304.0	0.22	0.1	0.1
-10.0	1.84	-11.60	3.44	15.04		32	304.0	2.21	0.7	0.7
-5.0	6.54	-6.60	8.14	14.74		34	323.0	6.52	2.0	1.9
-3.0	8.21	-4.60	9.81	14.41		35	332.5	9.57	2.9	2.8
-1.0	9.80	-2.60	11.40	14.00		38	361.0	13.80	3.8	3.7
1.0	11.35	-0.60	12.95	13.55		42	399.0	19.72	4.9	4.7
2.0	12.00	0.40	13.60	13.20		45	427.5	22.91	5.4	5.1
3.0	12.90	1.40	14.50	13.10		48	456.0	28.18	6.2	5.9
4.0	13.70	2.40	15.30	12.90		51	484.5	33.88	7.0	6.6
5.0	14.40	3.40	16.00	12.60		55	522.5	39.81	7.6	7.2
6.0	15.00	4.40	16.60	12.20		59	560.5	45.71	8.2	7.7
7.0	15.50	5.40	17.10	11.70		63	598.5	51.29	8.6	8.0

10 GHz		1-5 GHz Fall12 TQP13				4V ; 53 mA				
Die#1	Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(9.5V)	PDC(mw)	Pout(mw)	Drn Eff	PAE
-10.0	0.40	-12.55	2.95	15.50		33	313.5	1.97	0.6	0.6
-5.0	5.10	-7.55	7.65	15.20		34	323.0	5.82	1.8	1.7
-3.0	6.80	-5.55	9.35	14.90		36	342.0	8.61	2.5	2.4
-1.0	8.40	-3.55	10.95	14.50		38	361.0	12.45	3.4	3.3
1.0	9.90	-1.55	12.45	14.00		41	389.5	17.58	4.5	4.3
2.0	10.60	-0.55	13.15	13.70		43	408.5	20.65	5.1	4.8
3.0	11.30	0.45	13.85	13.40		45	427.5	24.27	5.7	5.4
4.0	12.10	1.45	14.65	13.20		48	456.0	29.17	6.4	6.1
5.0	12.80	2.45	15.35	12.90		51	484.5	34.28	7.1	6.7
6.0	13.50	3.45	16.05	12.60		55	522.5	40.27	7.7	7.3
7.0	13.95	4.45	16.50	12.05		59	560.5	44.67	8.0	7.5
8.0	14.45	5.45	17.00	11.55		62	589.0	50.12	8.5	7.9

Jason Hodkin Distributed Amp

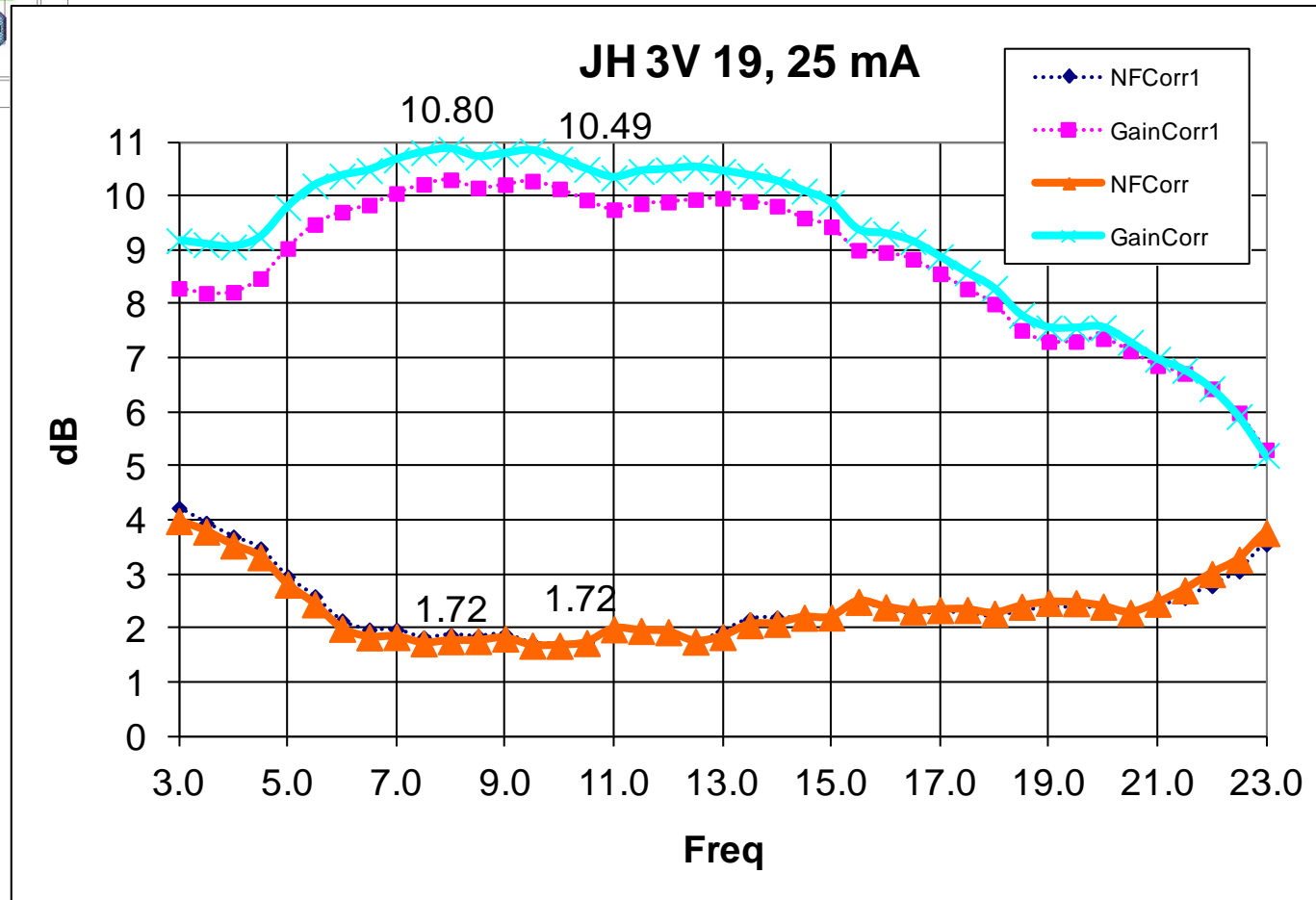
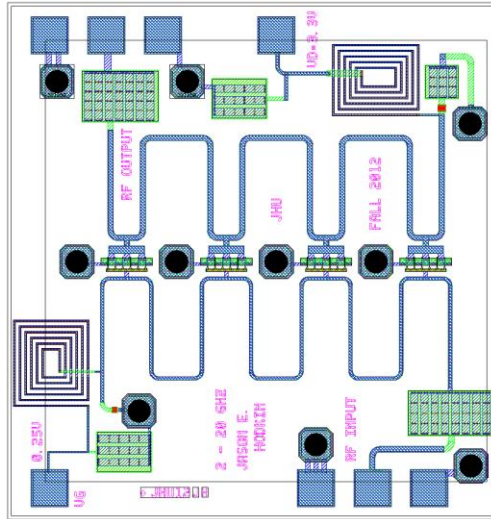
Very broadband gain, rolling off from a high of about 11 at 9 GHz to 7 dB at 20 GHz. Good noise figure (<2 dB) from 6 to 13 GHz.

JH2I25 2V 25mA

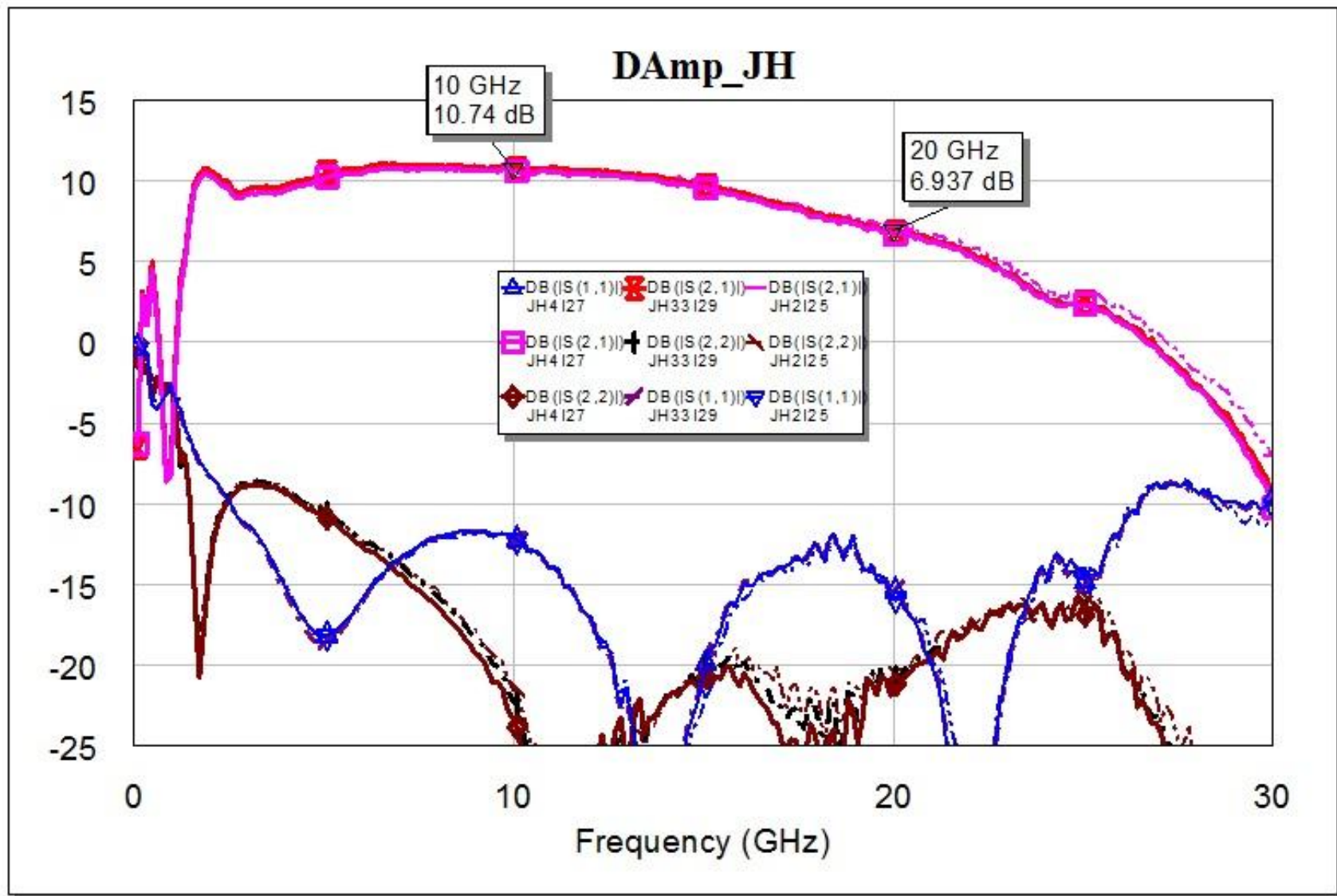
JH33I20 3.3V 20 mA vgs=0V

JH33I29 3.3V 29 mA vgs=0.2V

JH4I27 4.0V 27 mA vgs=0.2V



Jason Hodkin Distributed Amp



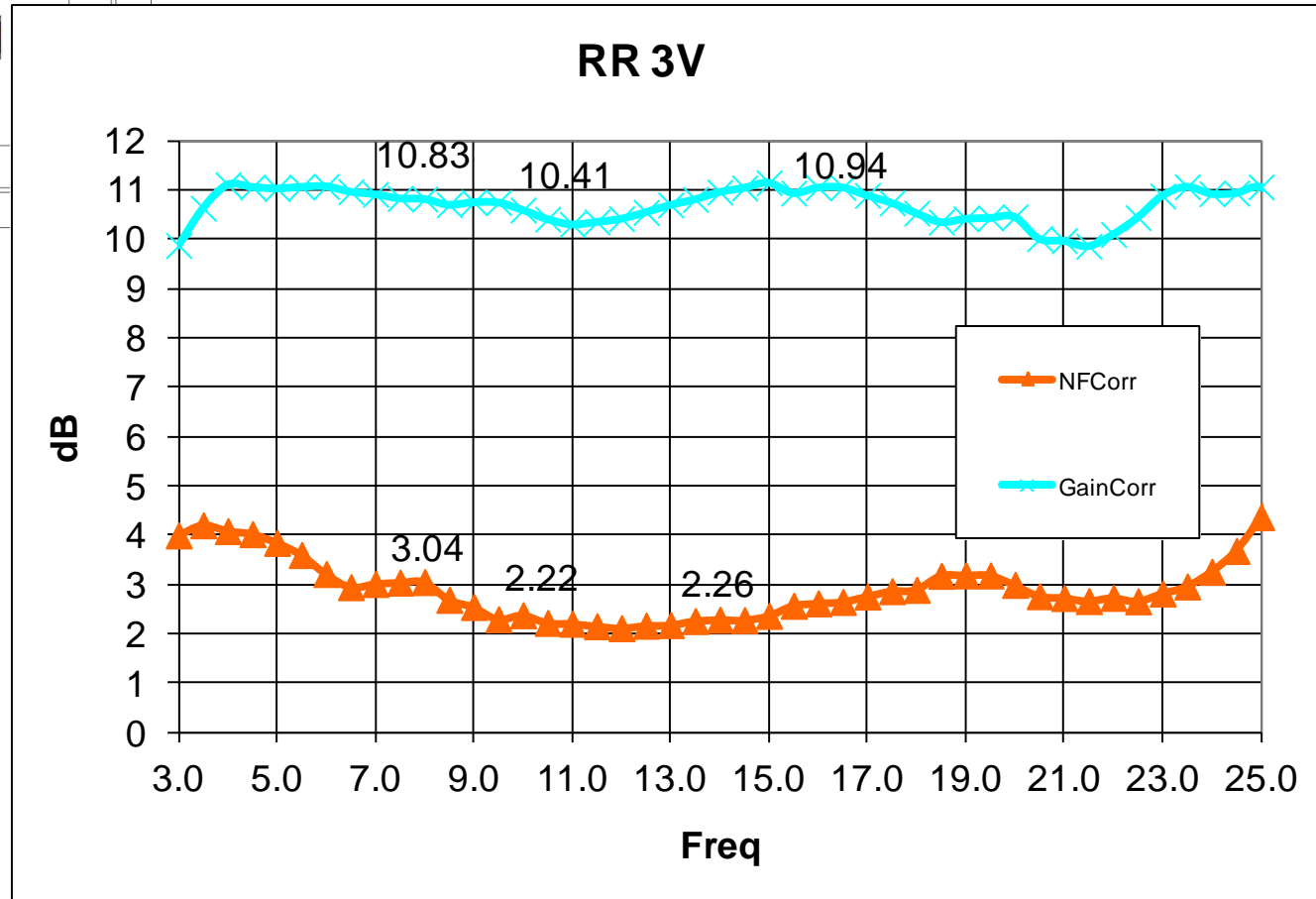
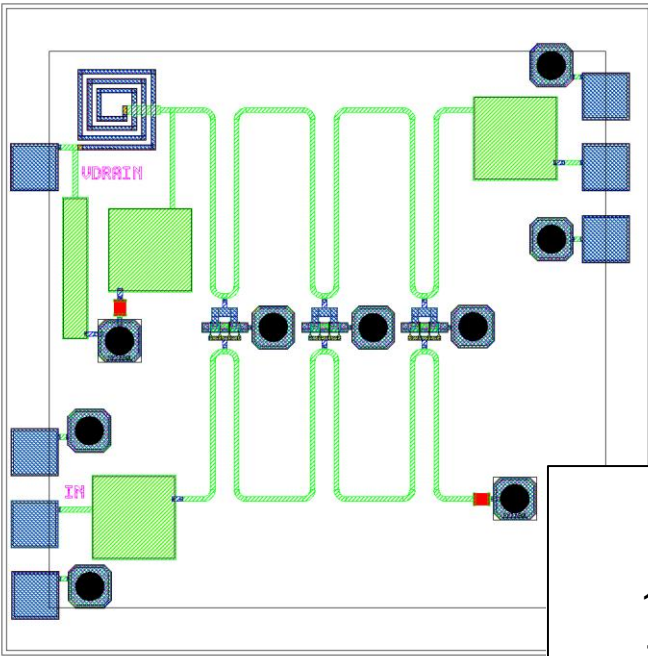
Robert Reyes Distributed Amp

Very broadband, flat gain of about 10 dB from 3-26 GHz. Good noise figure too.

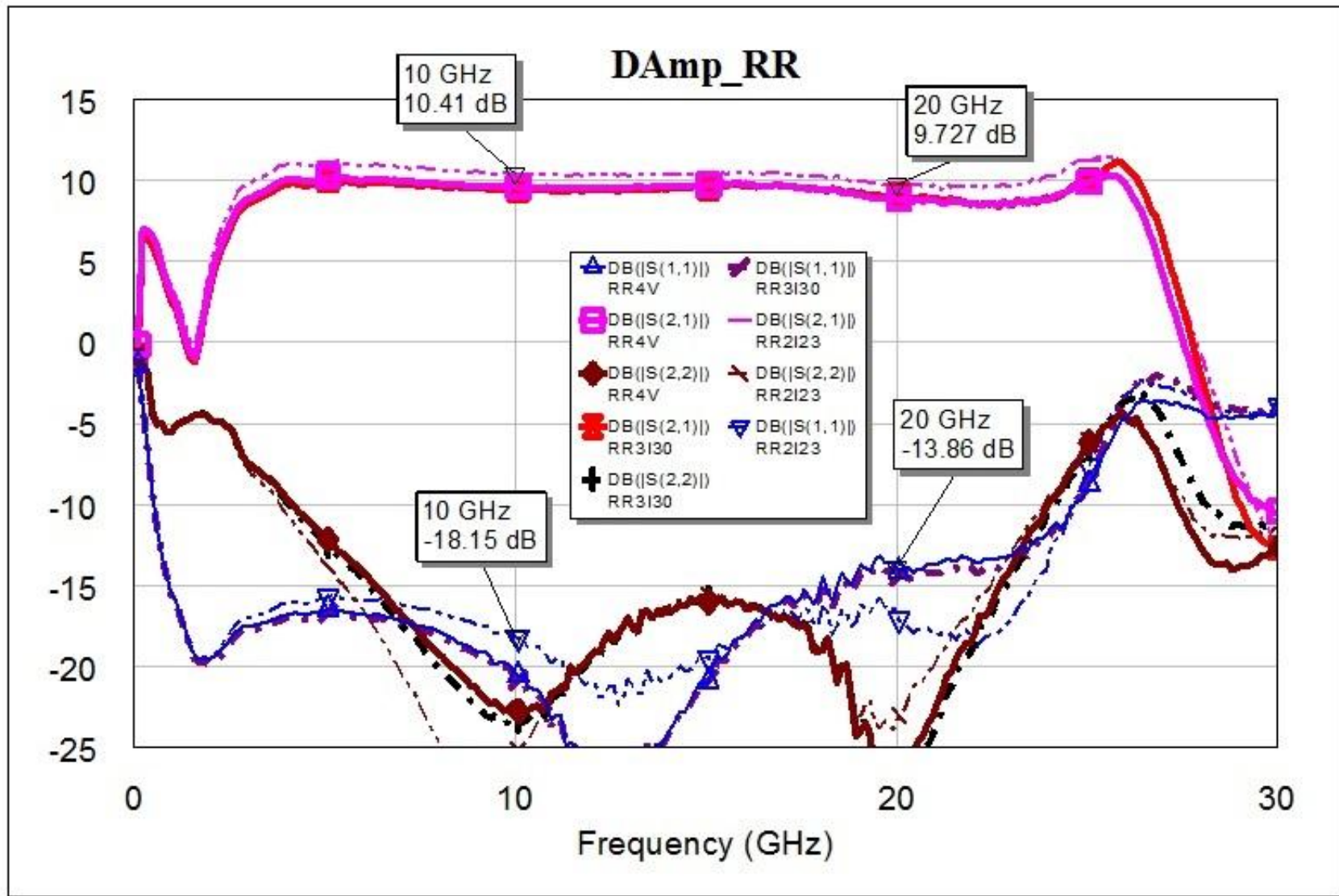
RR4V 4V 39 mA

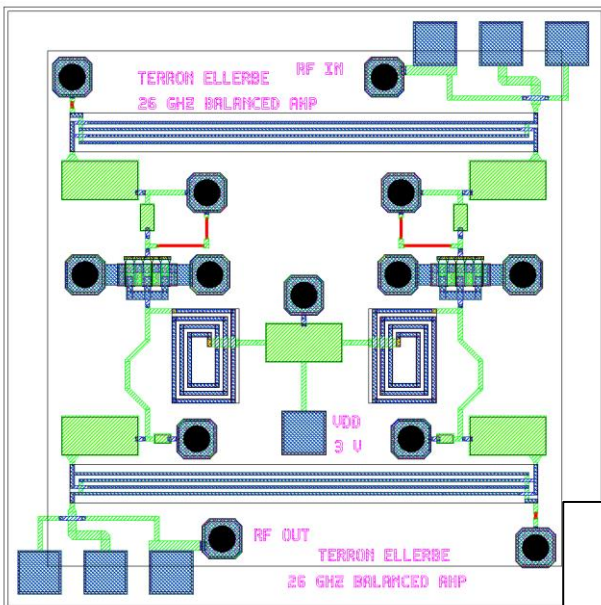
RR2I23 2V 23mA

RR3I30 3V 30mA



Robert Reyes Distributed Amp





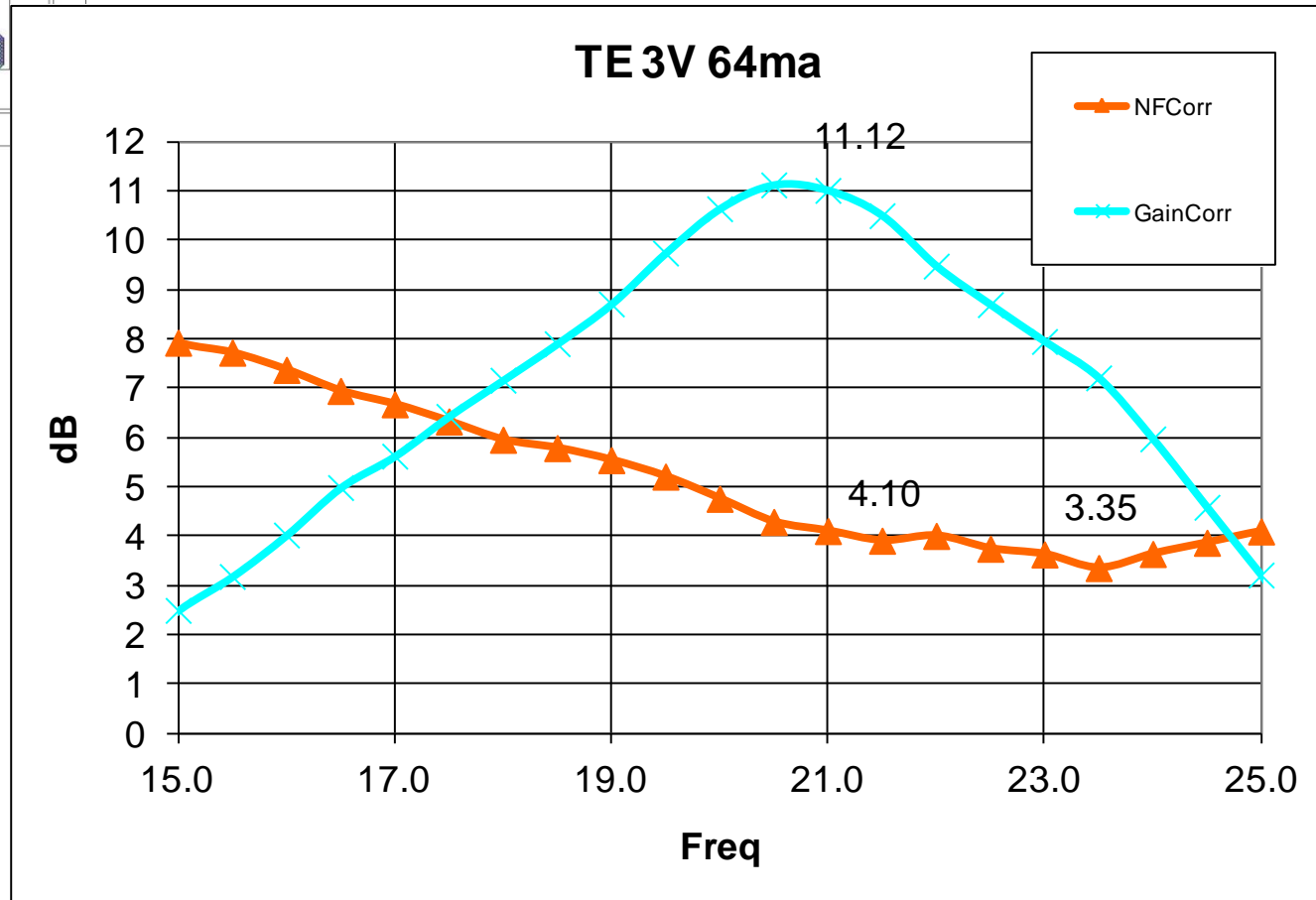
Terron Ellerbe Balanced Amp

The Balanced Amplifier worked well, but shifted down in frequency from the original design (26→21 GHz). Very typical result at these frequencies using standard microstrip models. An EM simulation would likely compare more closely with the measurements.

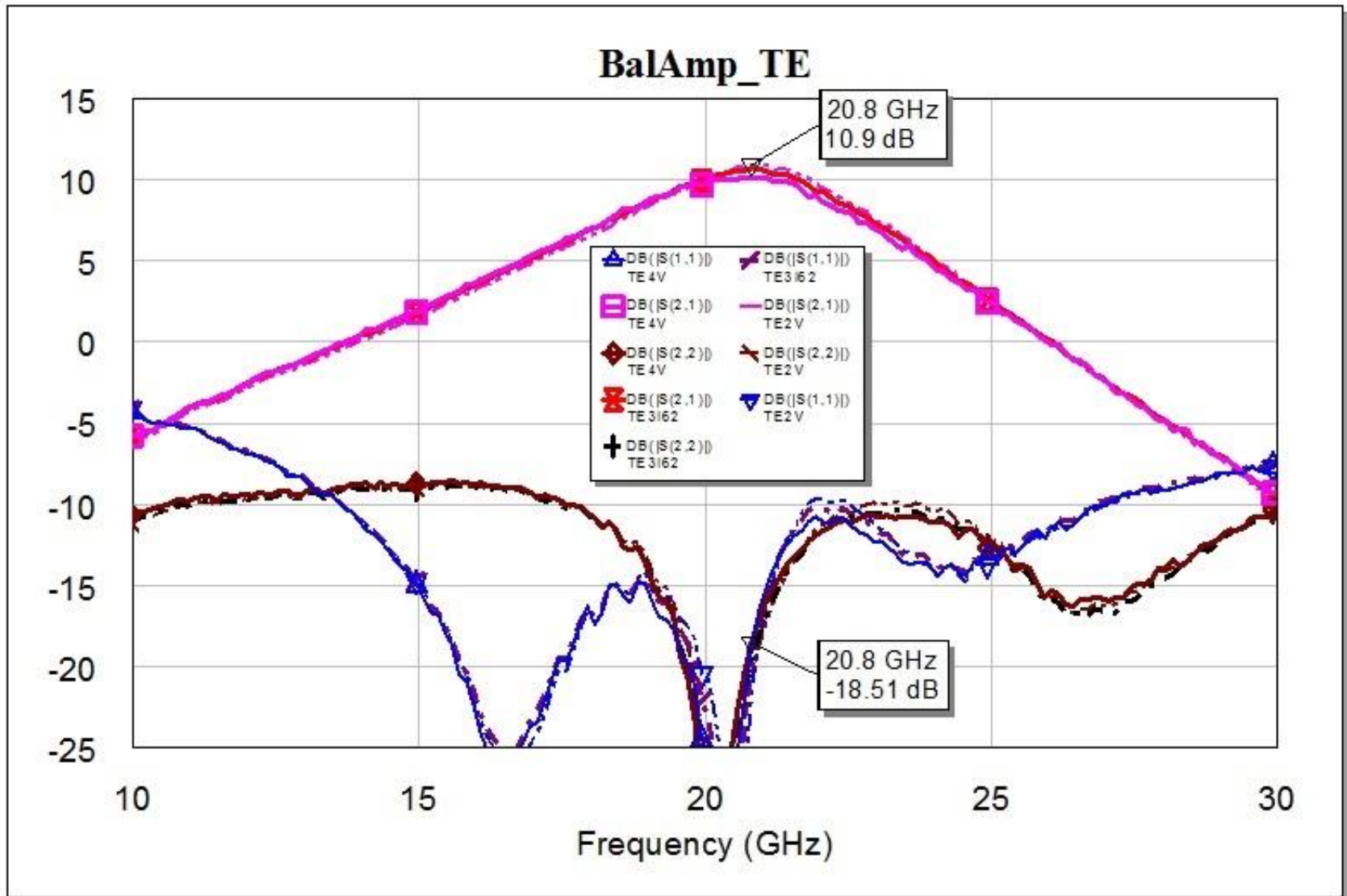
TE2V 2V 50 mA

TE3V 3V 62 mA

TE4V 4V 77 mA



Terron Ellerbe Balanced Amp



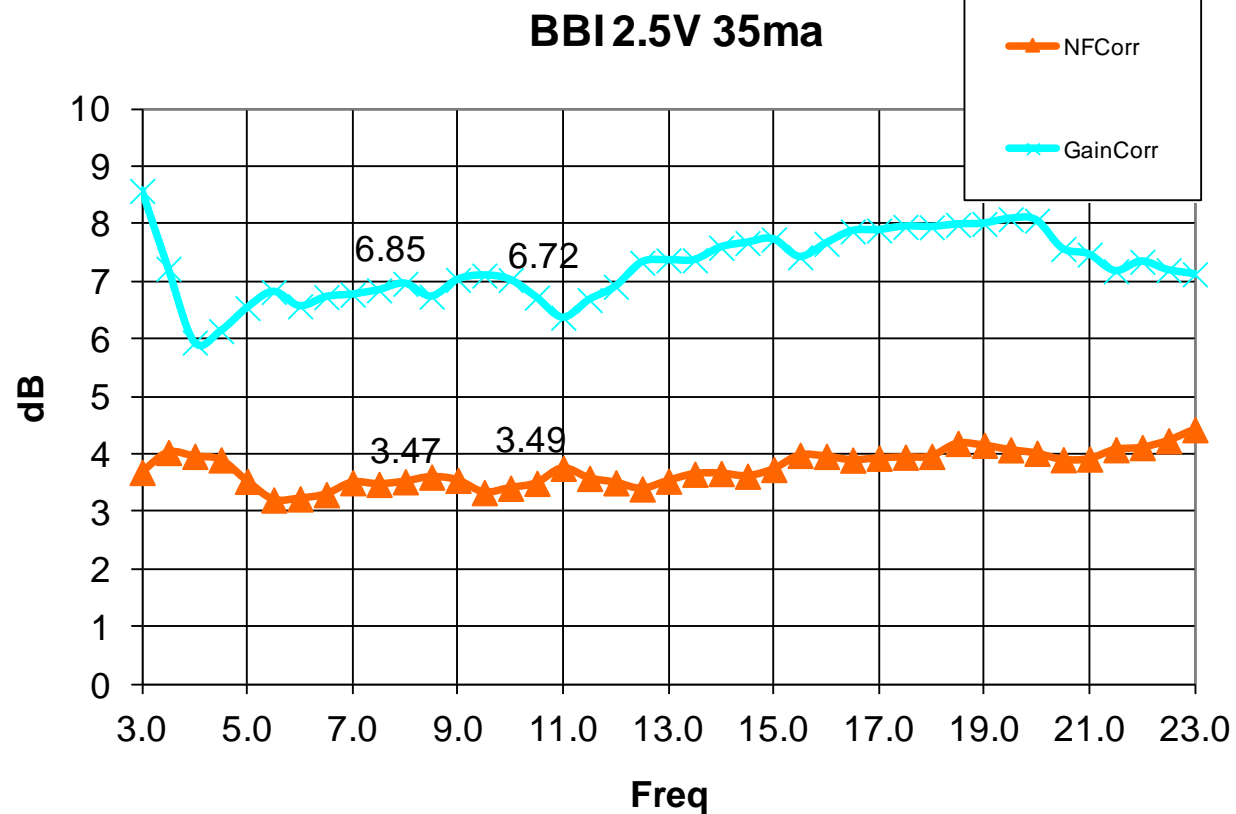
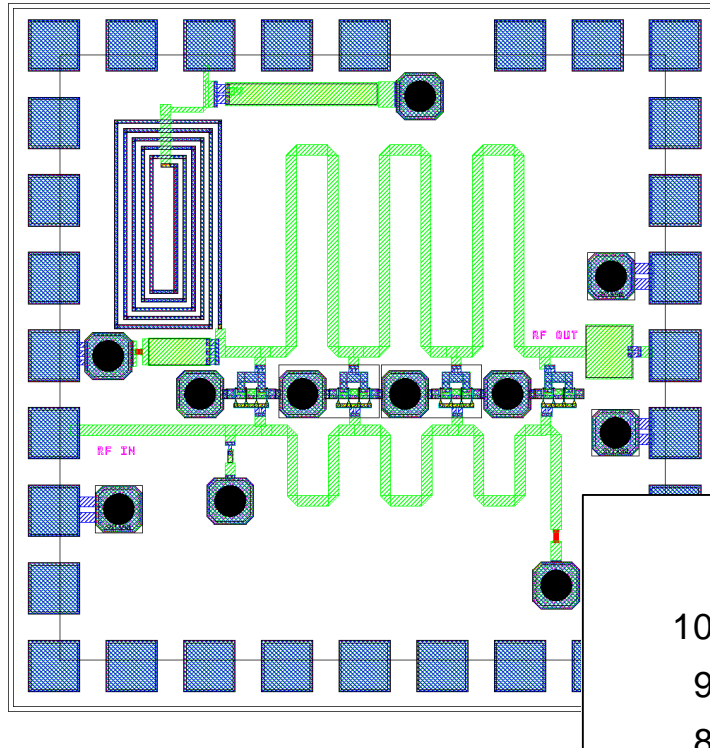
Brian Billman Balanced Amp

At higher DC biases, this design had a high frequency stability issue near 35 GHz, similar to the distributed amplifier problems noted in the Distributed Amplifier (John Penn, RF & Microwaves Magazine Feb 2013 article). Had fairly flat gain and good noise figure over a broad band.

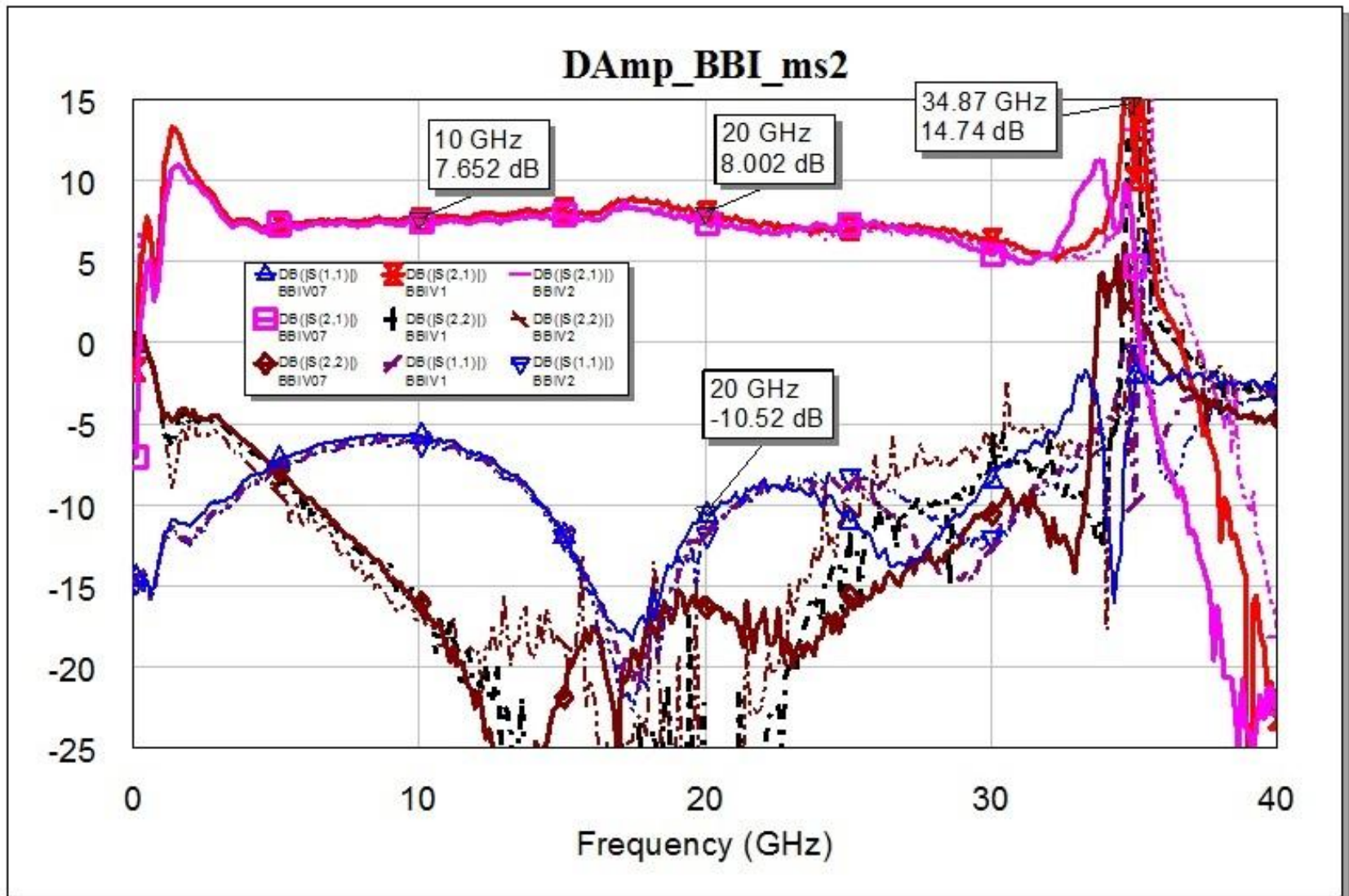
BBIV1_3 1.3V 27 mA

BBIV1_6 1.6V 29 mA

BBIV3_0 2.0V 31 mA



Brian Billman Balanced Amp



Michael Coon Low Noise Amp

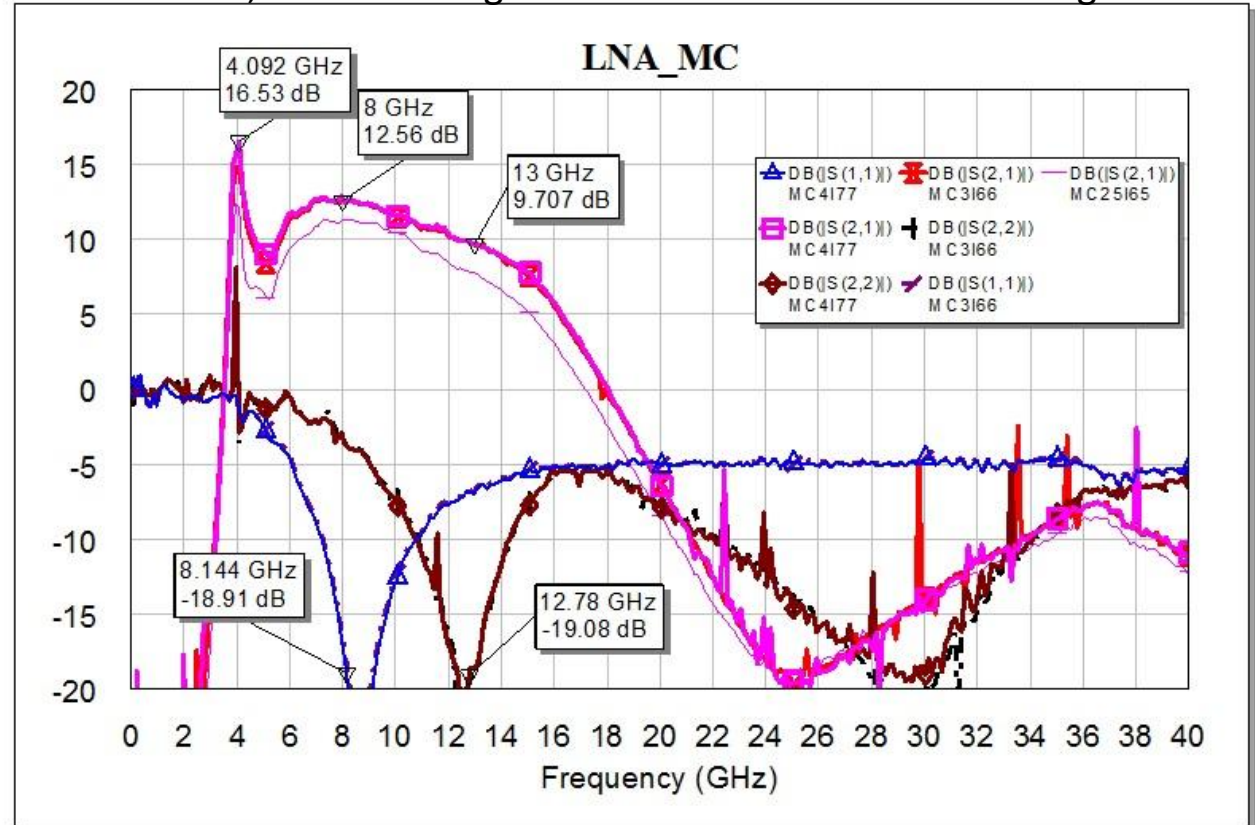
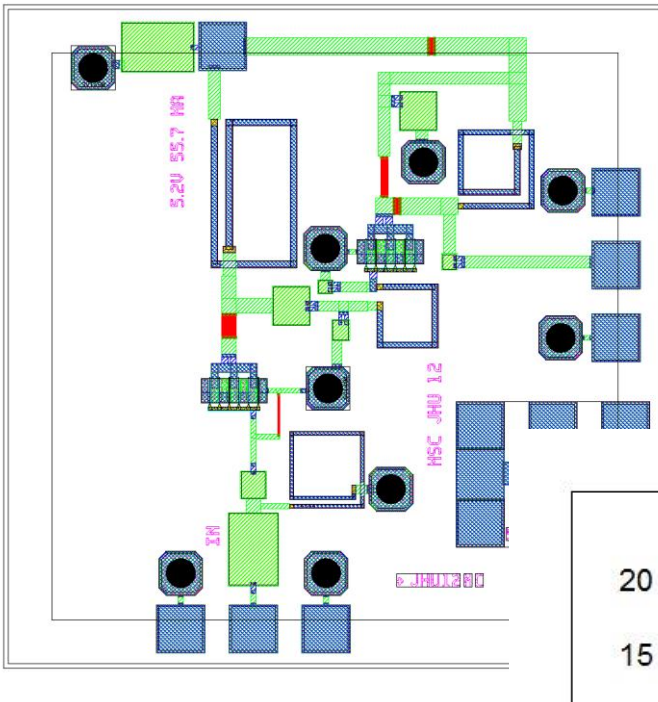
Some Low Frequency stability issues in test setup, but got some clean measurements at slightly lower DC bias points.

MC25165 2.5V 65 mA

MC3166 3.0V 66 mA

MC4167 4.0V 67 mA

Missed getting NF measurements. The NF meter failed during the testing, but later seemed to only have a problem at 3 GHz and below, so most designs were re-measured for Noise Figure.



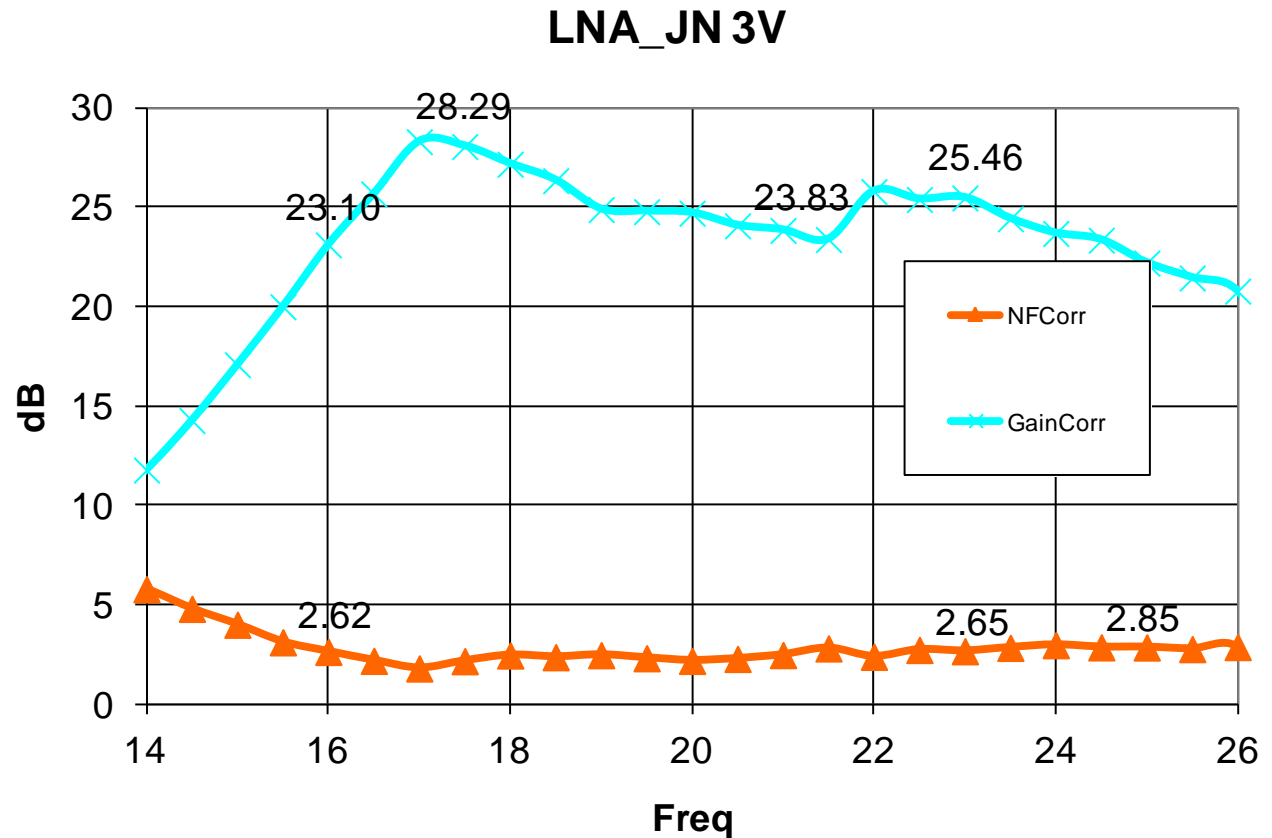
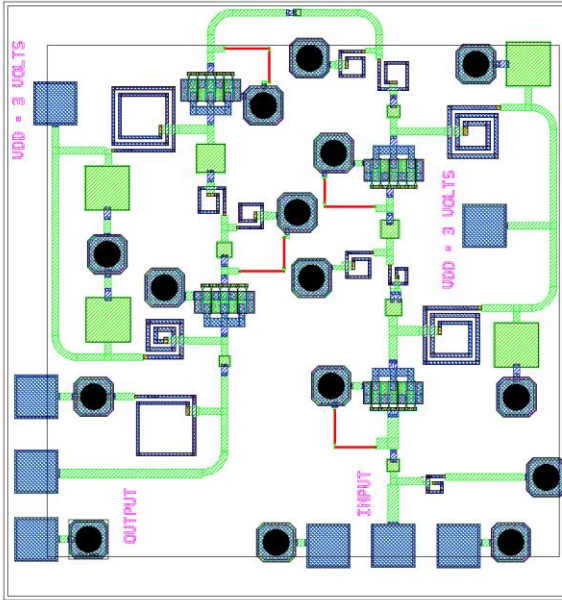
John Novak Broad Band Low Noise Amp

JN15I88 1.5V 88 mA

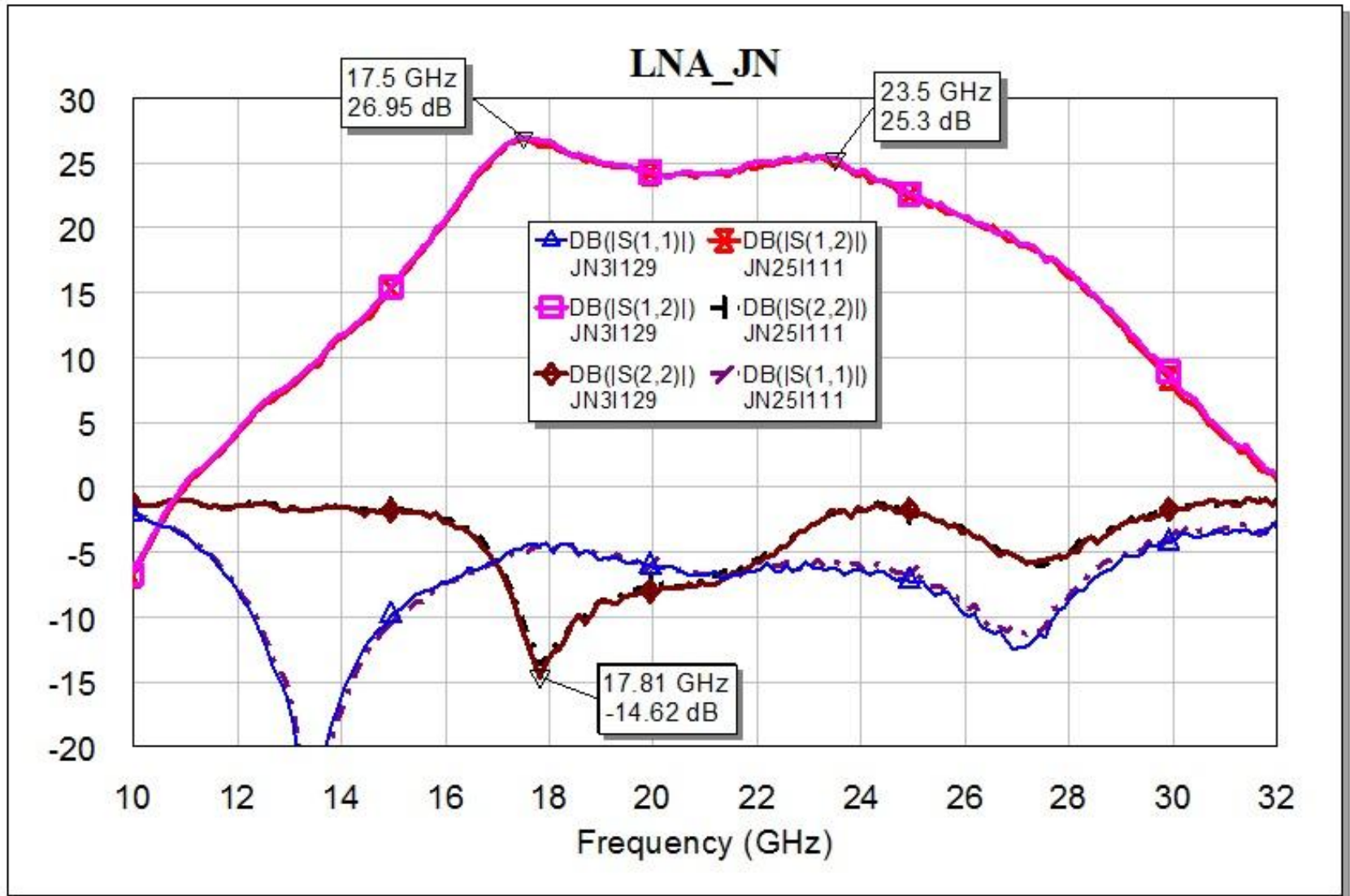
JN25I111 2.5V 111mA

JN3I139 3.0V 129 mA.

Measured s-parameters and noise figure of broadband LNA design. Very good gain over the band (~17-26 GHz) and good noise figure.



John Novak Broad Band Low Noise Amp



Shannon Marshall Distributed Amp

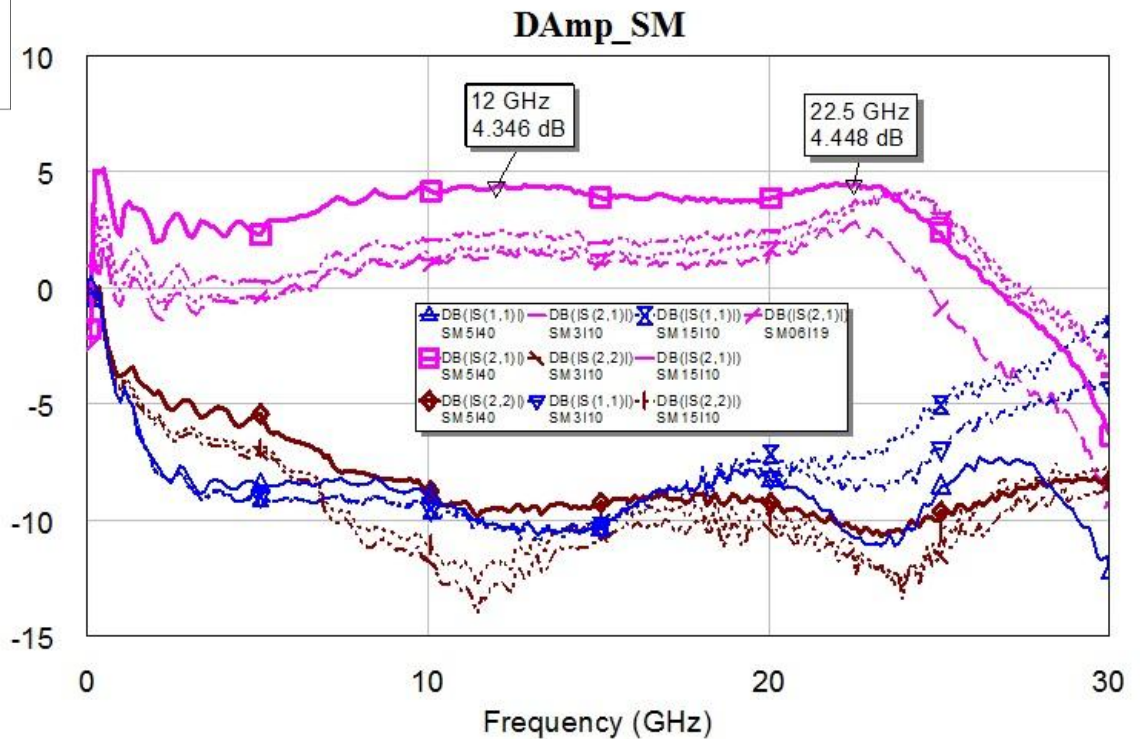
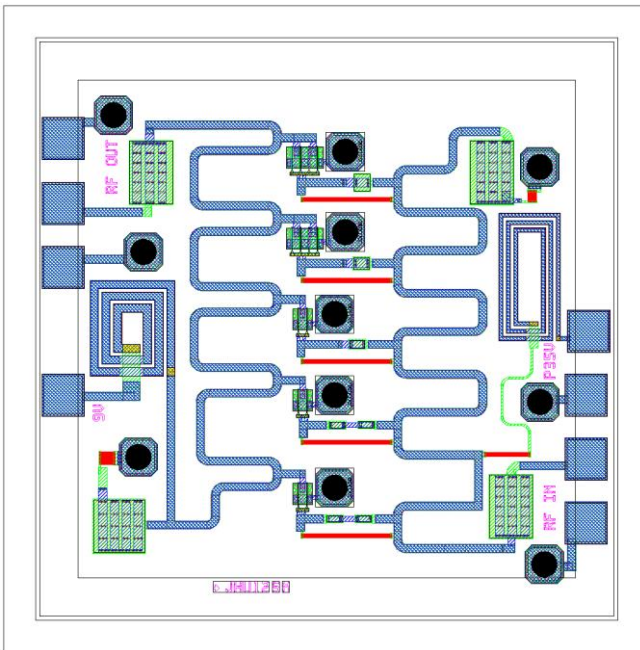
Low Frequency stability issue at 19-20 MHz in test setup!

SM3I10 3V 10 mA $v_{gs}=0$

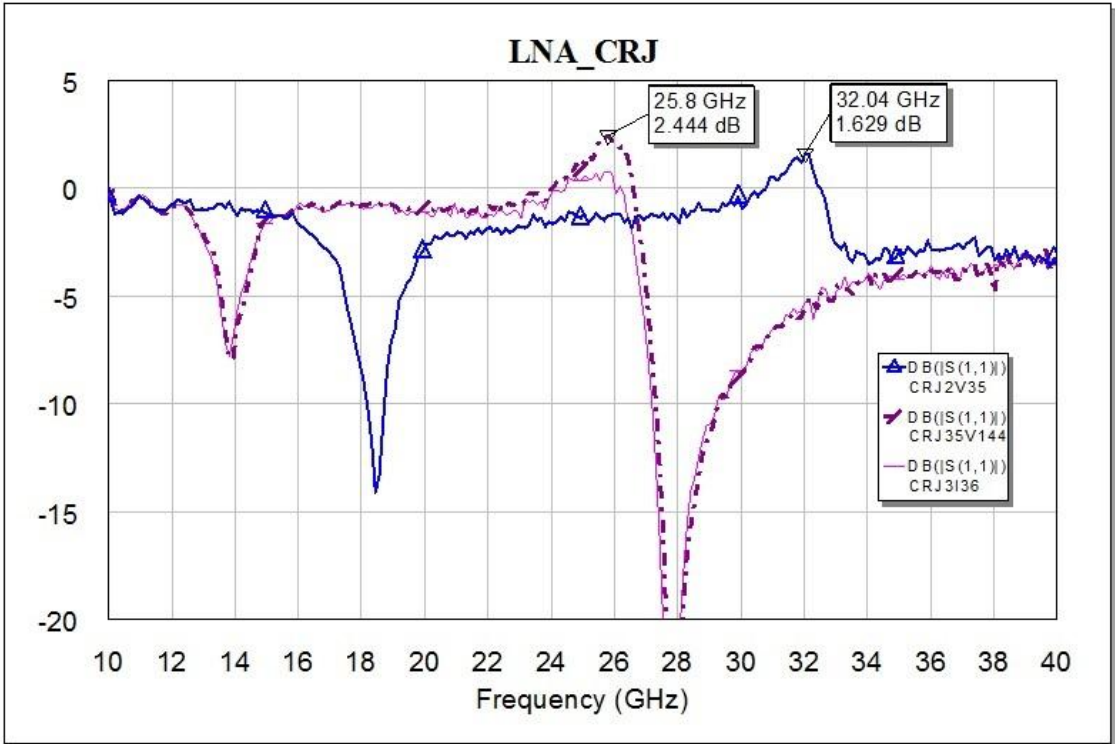
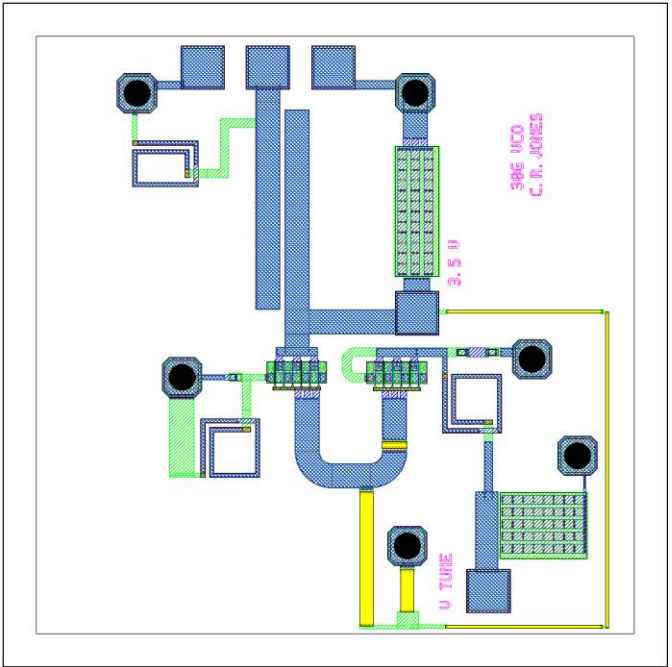
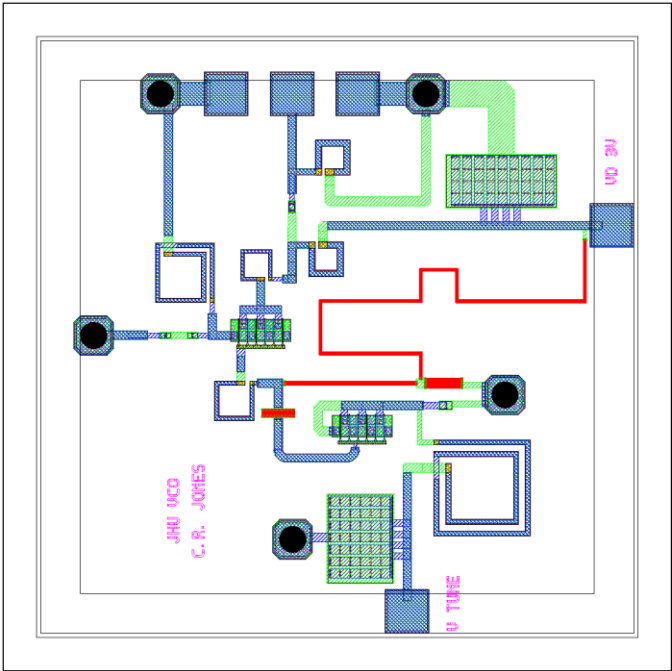
SM15I10 1.5V 10 mA $v_{gs}=0V$

SM06I10 0.6V 19 mA $v_{gs}=0.35V$

Got some Gain at lower DC biases, but could not seem to kill the low frequency oscillations in the probe setup—a common problem last year too. If 100 pf caps could be bonded close to the DC inputs, it would likely yield better gain.



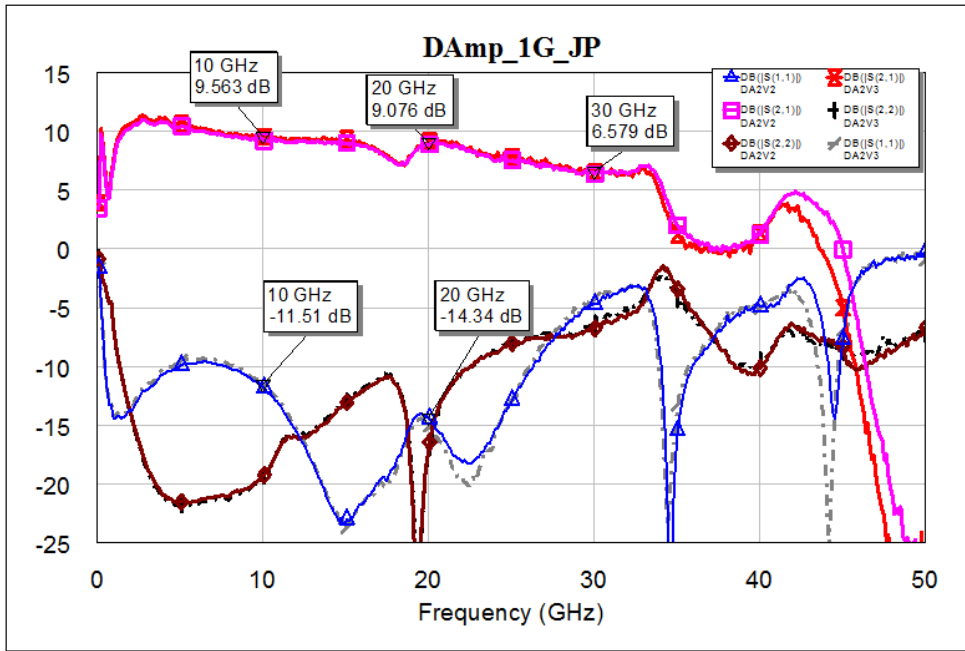
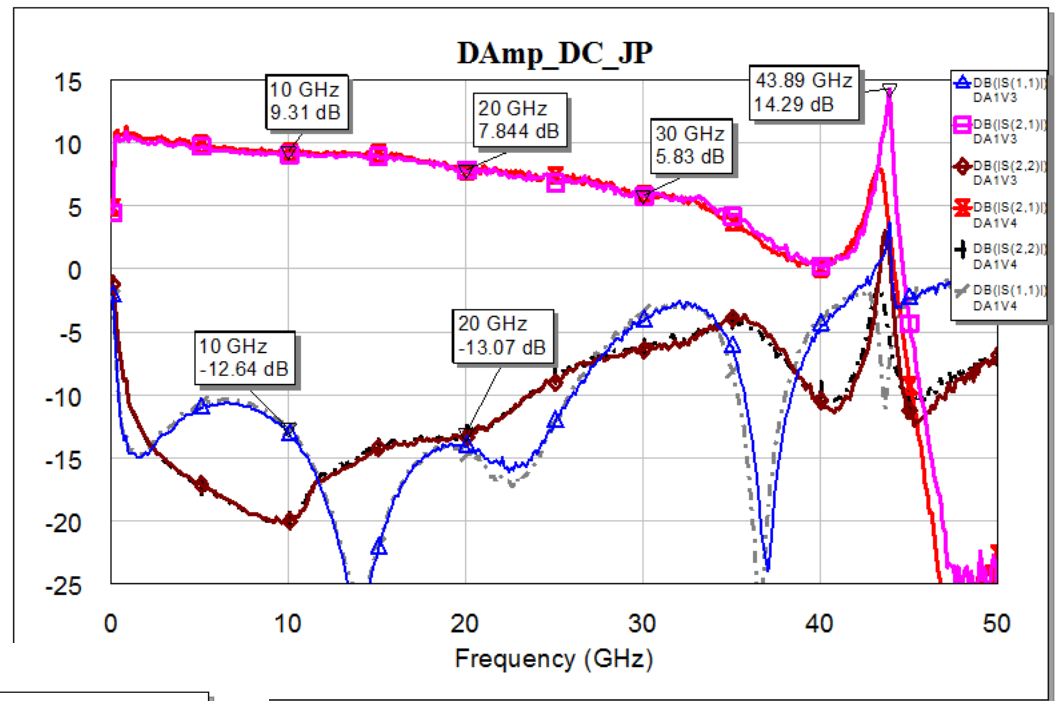
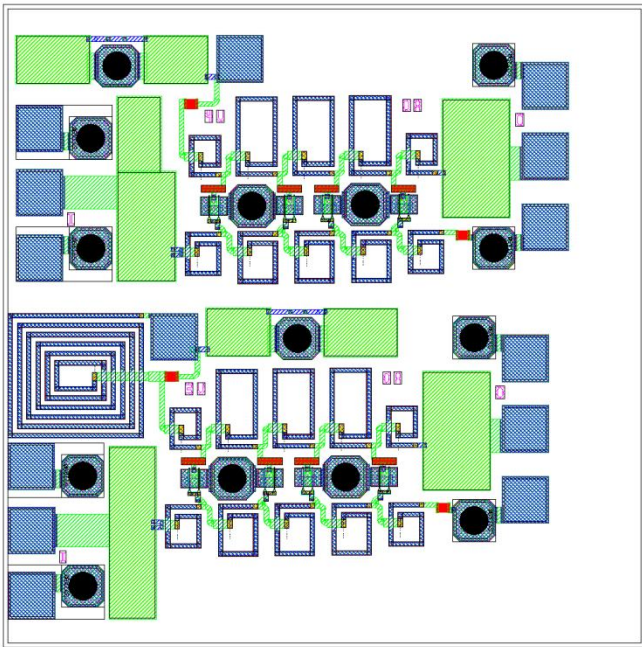
C. Reese Jones 30 GHz V1, V2 VCO



CRJ3I36 3.0V 36 mA

CRJ35I44 3.5V 44 mA

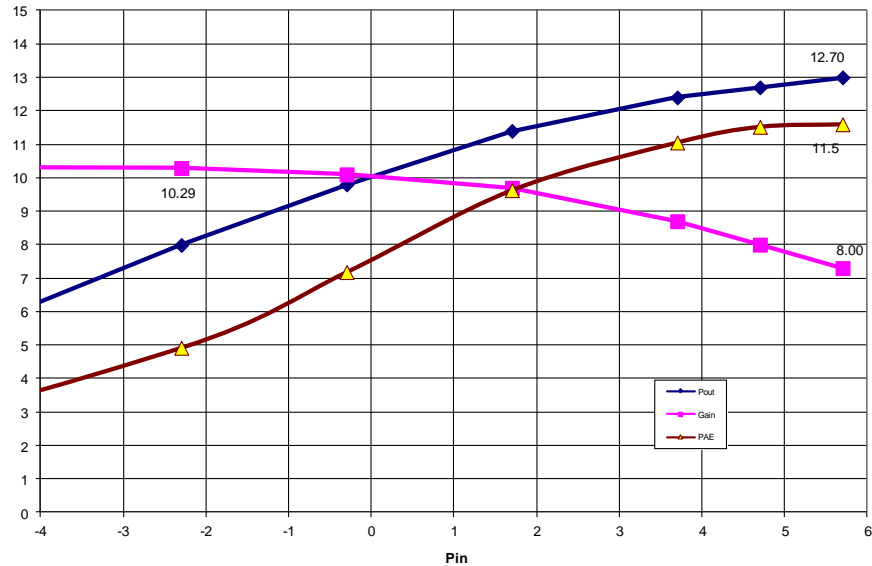
Measured on 8510, appears to have potential at ~26GHz for first design and ~32 GHz for second design. Tested first design with 26.5 GHz spectrum analyzer but did not seem to have enough gain to build up the oscillation. Noted previously that device gain might be too low at these frequencies for a VCO design, but it looks like it is close to oscillating.



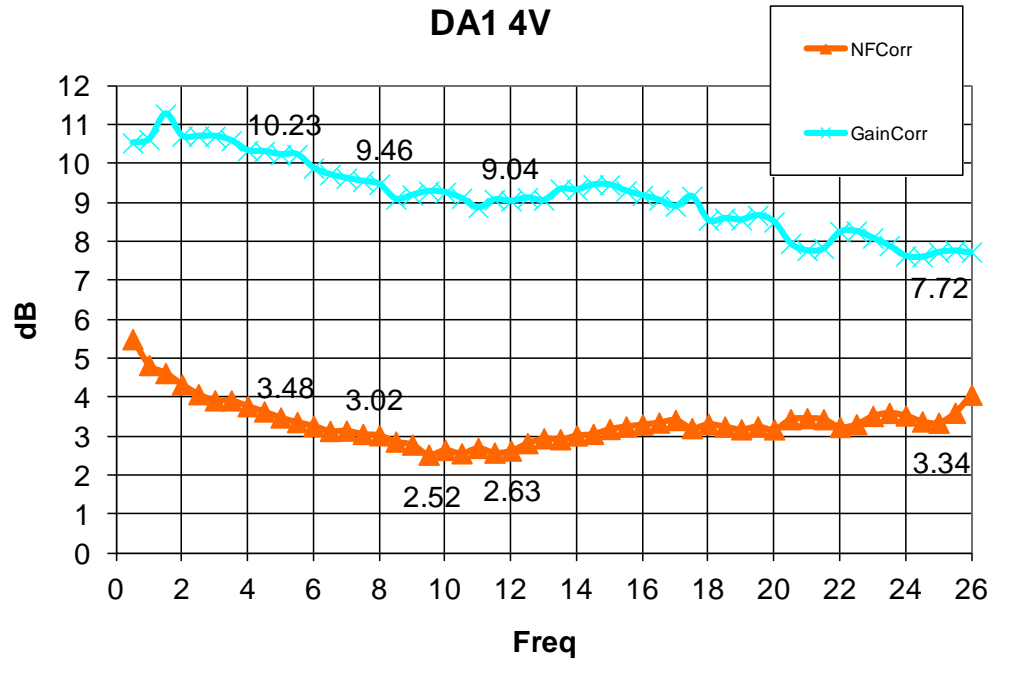
John Penn Distributed Amplifier (2011 revisited)

The original 2011 design inadvertently was fabbed without the intended 5Ω drain resistors. Article on 2011 design was in Feb 2013 RF & Microwaves Magazine. This 2012 “redo” had better stability, though the DC-30 GHz version still has a gain spike at 44 GHz.

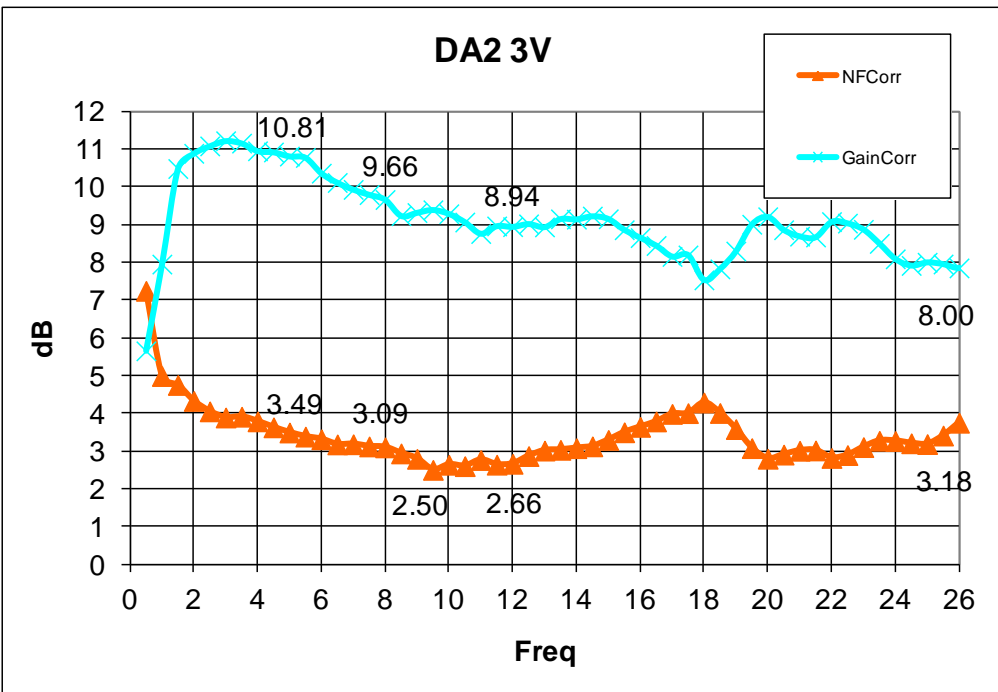
DA2 10GHz Meas 12
4V ~27mA



DA1 4V

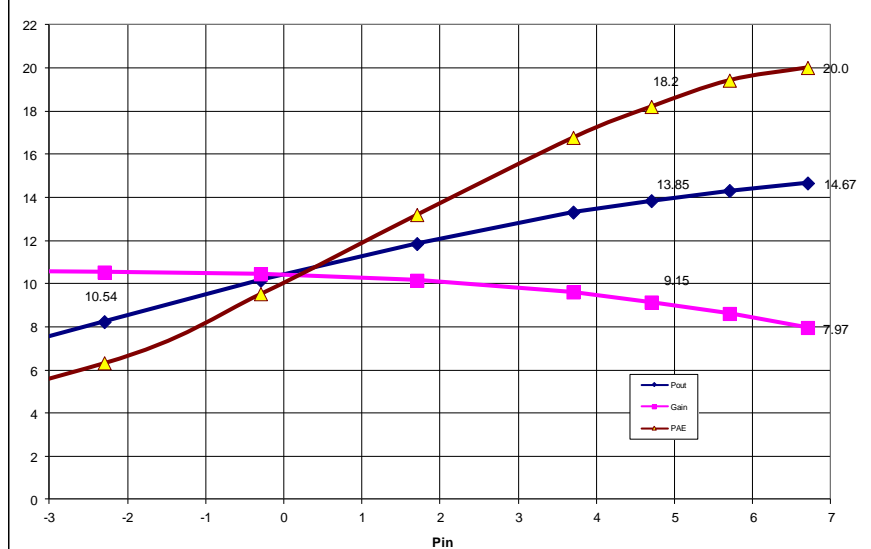


DA2 3V



John Penn Distributed Amplifier (2012)

DA1 10GHz Meas 12
3V ~30mA

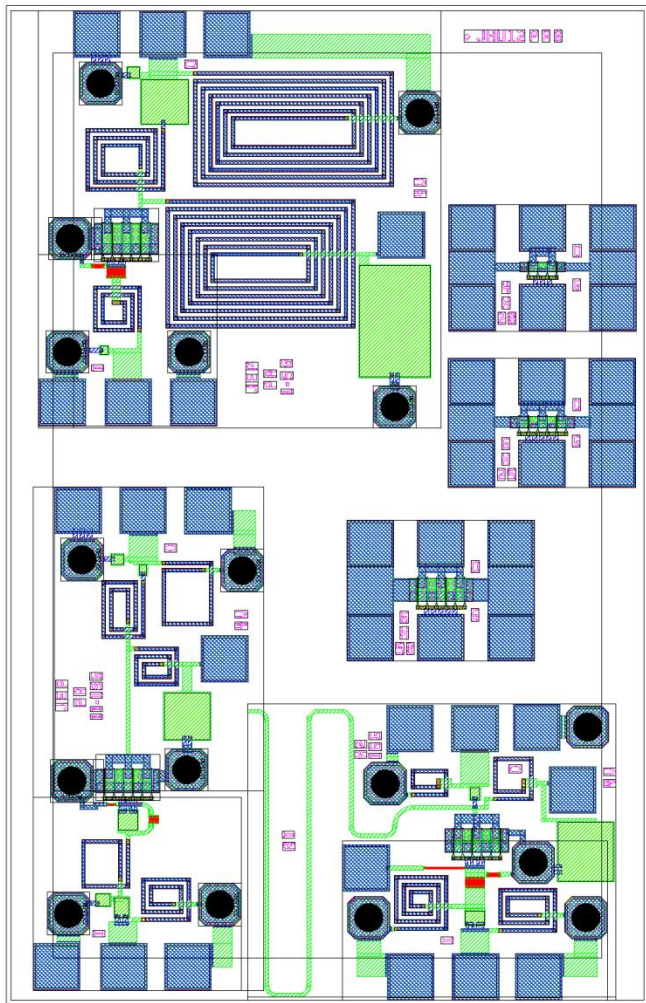


John Penn Distributed Amplifier Performance (2012)

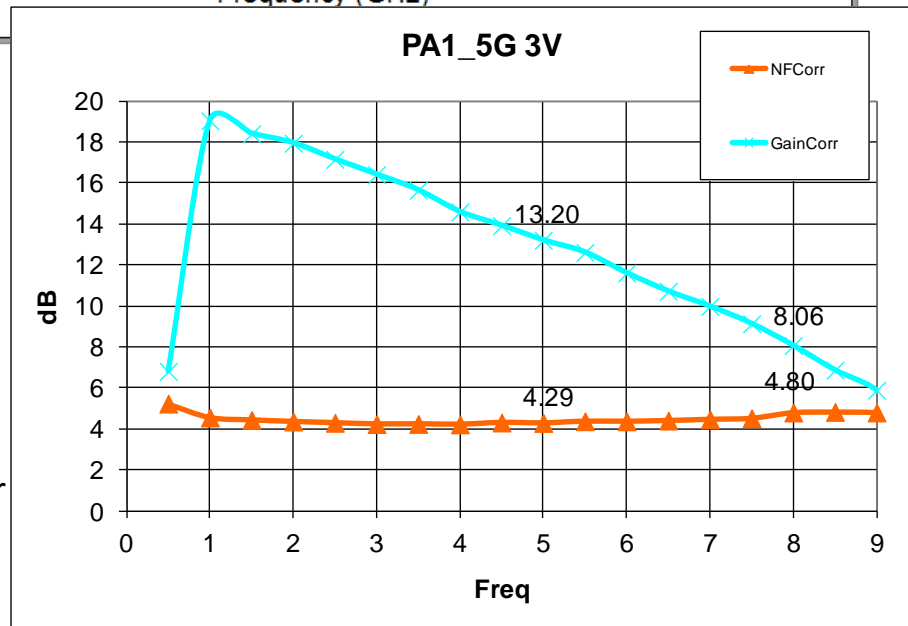
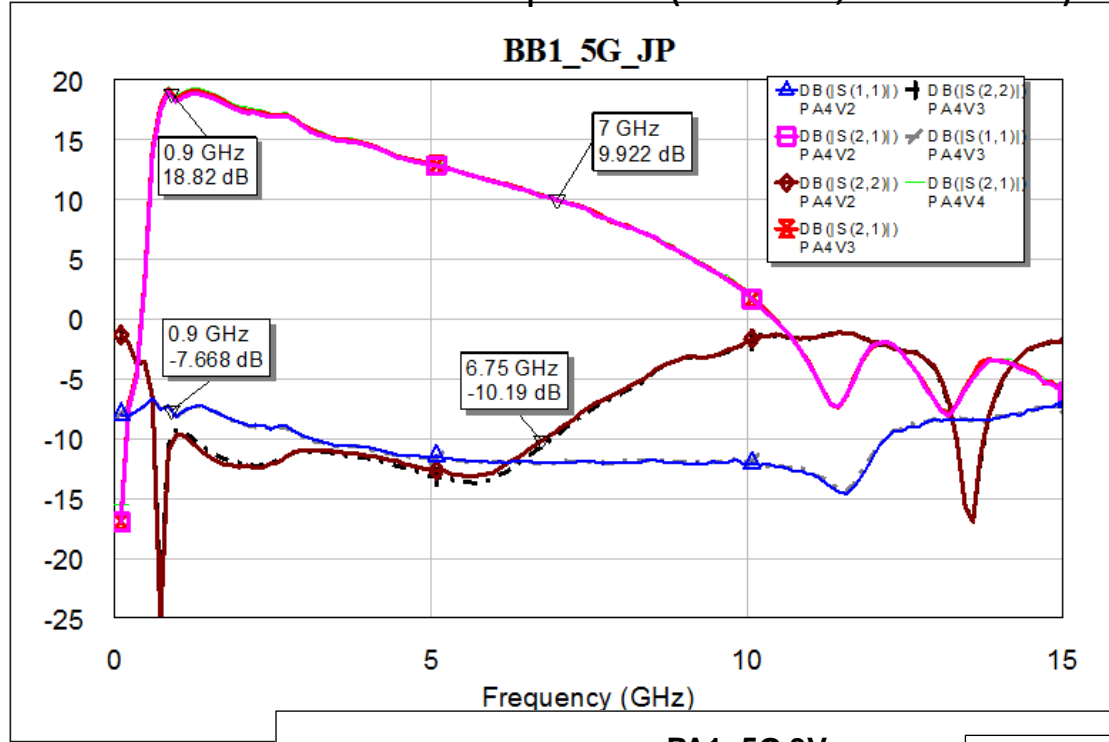
10 GHz	Die#1	DA1_2 4V 10 GHz Fall12 TQP13				4V ; 27 mA				
Pin(SG)	Pout(PM)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE	
-10.0	-4.20	-12.30	-1.90	10.40	27	108.0	0.65	0.6	0.5	
-5.0	0.72	-7.30	3.02	10.32	27	108.0	2.00	1.9	1.7	
0.0	5.69	-2.30	7.99	10.29	29	116.0	6.30	5.4	4.9	
2.0	7.50	-0.30	9.80	10.10	30	120.0	9.55	8.0	7.2	
4.0	9.10	1.70	11.40	9.70	32	128.0	13.80	10.8	9.6	
6.0	10.10	3.70	12.40	8.70	34	136.0	17.38	12.8	11.1	
7.0	10.40	4.70	12.70	8.00	34	136.0	18.62	13.7	11.5	
8.0	10.70	5.70	13.00	7.30	35	140.0	19.95	14.3	11.6	

10 GHz	Die#1	DA2_1 3V 10 GHz Fall12 TQP13				3V ; 30 mA				
Pin(SG)	Pout(PM)	Pin(corr)	Pout(corr)	Gain	I1(3V)	PDC(mw)	Pout(mw)	Drn Eff	PAE	
-10.0	-3.80	-12.30	-1.50	10.80	30	90.0	0.71	0.8	0.7	
-5.0	1.10	-7.30	3.40	10.70	31	93.0	2.19	2.4	2.2	
0.0	5.94	-2.30	8.24	10.54	32	96.0	6.67	6.9	6.3	
2.0	7.86	-0.30	10.16	10.46	33	99.0	10.38	10.5	9.5	
4.0	9.56	1.70	11.86	10.16	35	105.0	15.35	14.6	13.2	
6.0	11.02	3.70	13.32	9.62	38	114.0	21.48	18.8	16.8	
7.0	11.55	4.70	13.85	9.15	39	117.0	24.27	20.7	18.2	
8.0	12.02	5.70	14.32	8.62	40	120.0	27.04	22.5	19.4	
9.0	12.37	6.70	14.67	7.97	41	123.0	29.31	23.8	20.0	

John Penn BroadBand Amplifiers (1-5 GHz, 11-19 GHz)

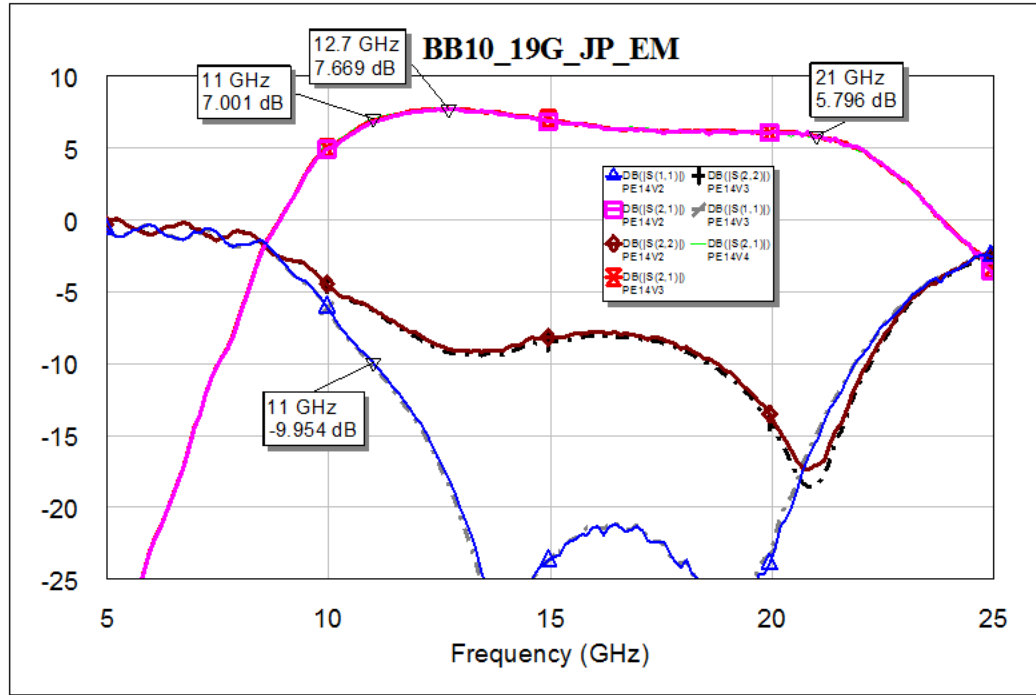
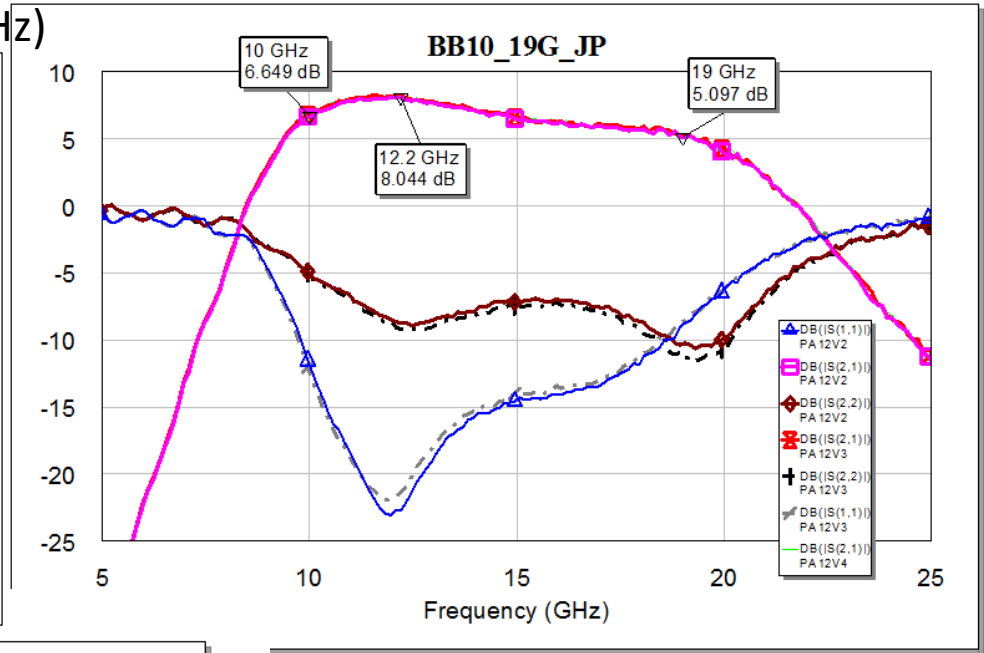
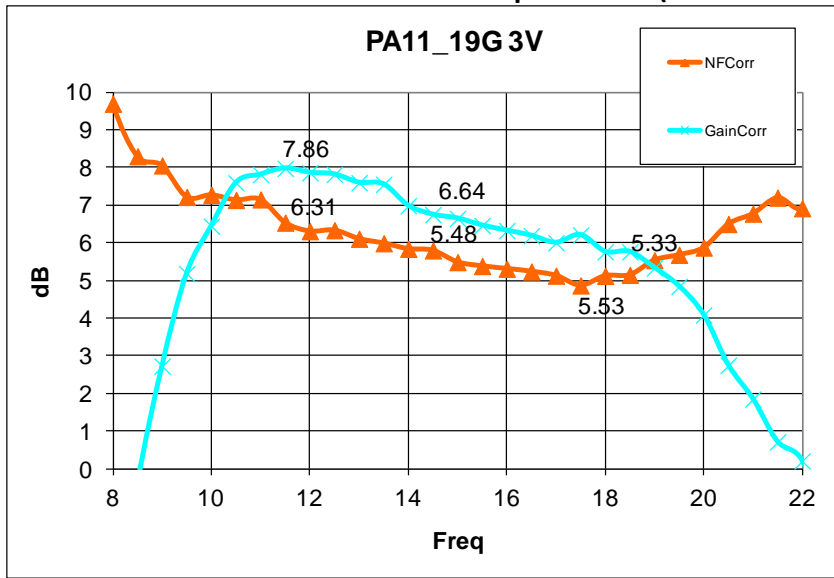


- Broadband PA 1-5 GHz (1)
- PA4V2 2V 38 mA --Die #1
- PA4V3 3V 45 mA --Die #1
- PA4V4 4V 55 mA --Die #1
- Broadband PA 11-19 GHz (2)
- PA12V2 2V 29 mA --Die #1
- PA12V3 3V 36 mA --Die #1
- PA12V4 4V 43 mA --Die #1



Note: designed for Power, not NF.

John Penn BroadBand Amplifiers (11-19 GHz)

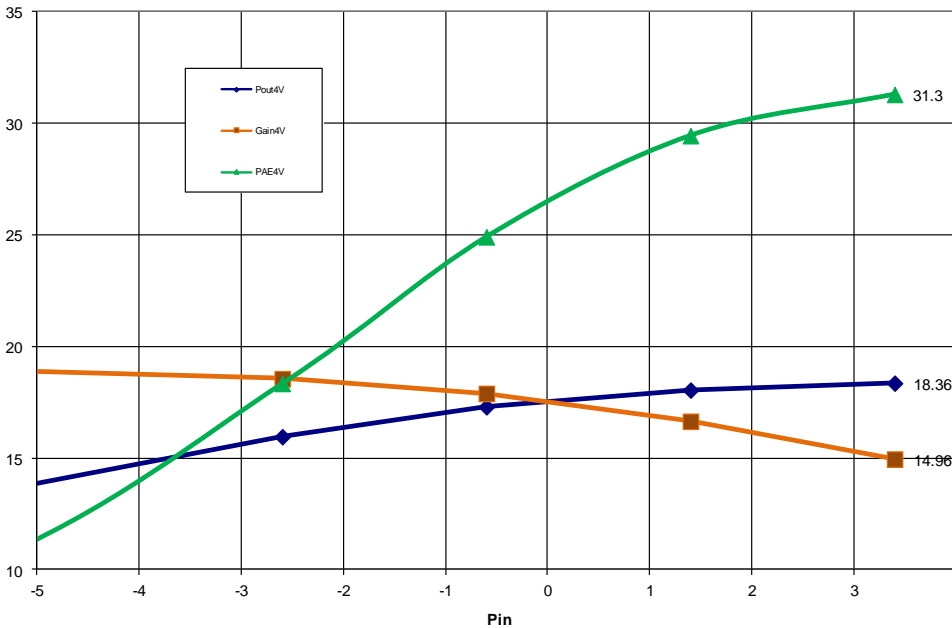


Two Versions—one “EM tuned” (11-21 GHz) to offset expected down shift in frequency from nominal models (10-19 GHz). Designed for broadband power and efficiency, not noise figure.

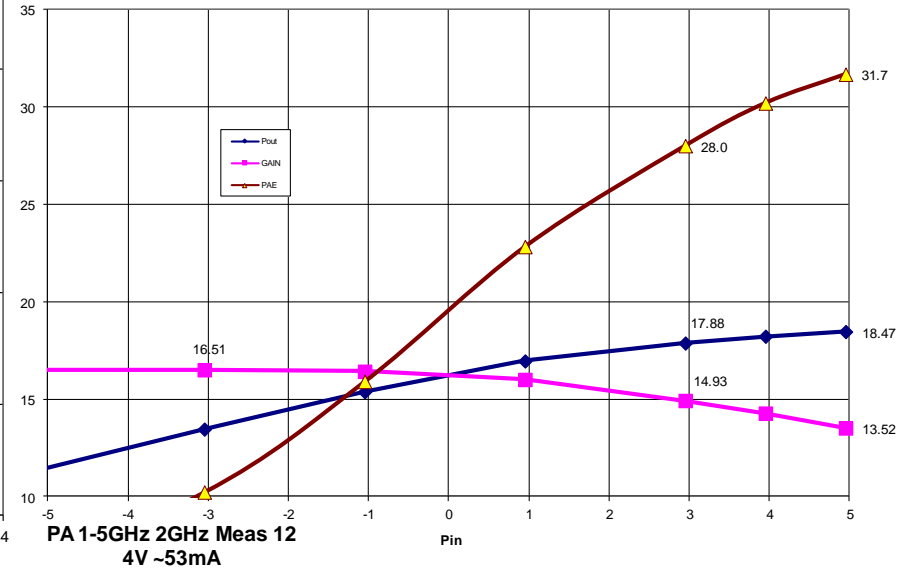
Broadband PA 11-19 GHz (2)
 PA12V2 2V 29 mA --Die #1
 PA12V3 3V 36 mA --Die #1
 PA12V4 4V 43 mA --Die #1

John Penn BroadBand Amplifiers (1-5 GHz)

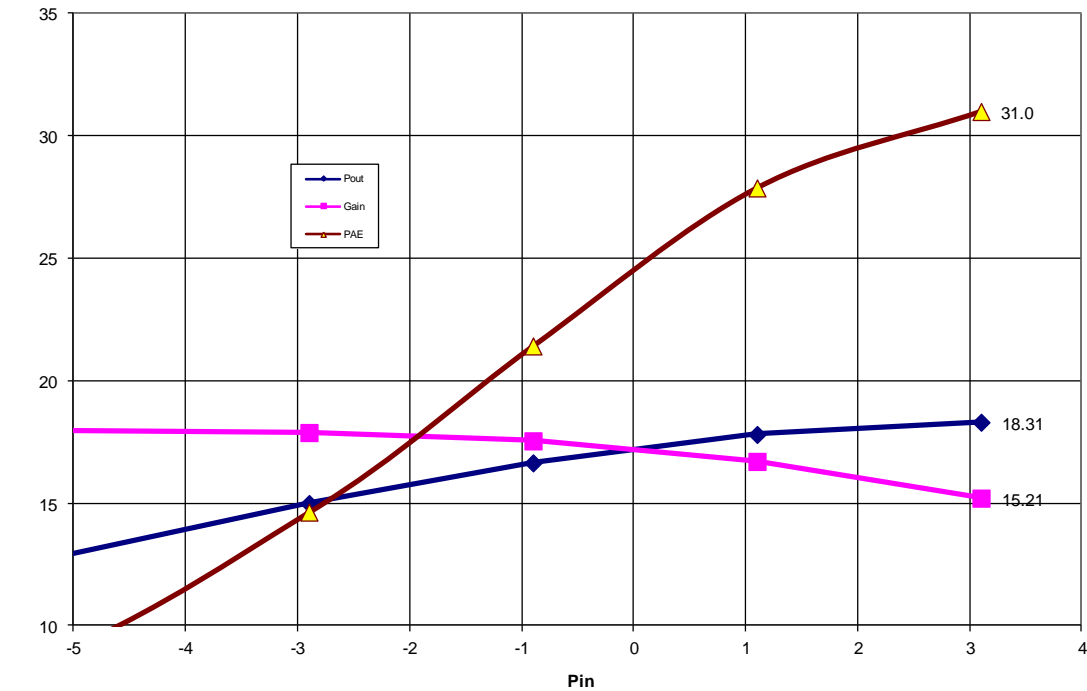
PA 1-5GHz 1GHz Meas 12
4V ~53mA



PA 1-5GHz 3GHz Meas 12
4V ~53mA



PA 1-5GHz 2GHz Meas 12
4V ~53mA



John Penn BroadBand Amplifiers (1-5 GHz)

1 GHz	Die#1	1-5 GHz Fall12 TQP13				4V ; 53 mA			
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE
-10.0	7.78	-10.60	8.38	18.98	53	212.0	6.89	3.2	3.2
-5.0	12.77	-5.60	13.37	18.97	53	212.0	21.73	10.2	10.1
-2.0	15.36	-2.60	15.96	18.56	53	212.0	39.45	18.6	18.3
0.0	16.70	-0.60	17.30	17.90	53	212.0	53.70	25.3	24.9
2.0	17.45	1.40	18.05	16.65	53	212.0	63.83	30.1	29.5
4.0	17.76	3.40	18.36	14.96	53	212.0	68.55	32.3	31.3

2 GHz	Die#1	1-5 GHz Fall12 TQP13				4V ; 53 mA			
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE
-10.0	6.13	-10.90	7.03	17.93	53	212.0	5.05	2.4	2.3
-5.0	11.19	-5.90	12.09	17.99	53	212.0	16.18	7.6	7.5
-2.0	14.09	-2.90	14.99	17.89	53	212.0	31.55	14.9	14.6
0.0	15.75	-0.90	16.65	17.55	53	212.0	46.24	21.8	21.4
2.0	16.91	1.10	17.81	16.71	53	212.0	60.39	28.5	27.9
4.0	17.41	3.10	18.31	15.21	53	212.0	67.76	32.0	31.0

3 GHz	Die#1	1-5 GHz Fall12 TQP13				4V ; 53 mA			
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE
-10.0	4.33	-11.05	5.38	16.43	53	212.0	3.45	1.6	1.6
-5.0	9.40	-6.05	10.45	16.50	53	212.0	11.09	5.2	5.1
-2.0	12.41	-3.05	13.46	16.51	53	212.0	22.18	10.5	10.2
0.0	14.33	-1.05	15.38	16.43	53	212.0	34.51	16.3	15.9
2.0	15.91	0.95	16.96	16.01	53	212.0	49.66	23.4	22.8
4.0	16.83	2.95	17.88	14.93	53	212.0	61.38	29.0	28.0
5.0	17.18	3.95	18.23	14.28	53	212.0	66.53	31.4	30.2
6.0	17.42	4.95	18.47	13.52	53	212.0	70.31	33.2	31.7
2.0	16.02	0.95	17.07	16.12	53	212.0	50.93	24.0	23.4
4.0	17.21	2.95	18.26	15.31	53	212.0	66.99	31.6	30.7
5.0	17.56	3.95	18.61	14.66	53	212.0	72.61	34.3	33.1
6.0	17.80	4.95	18.85	13.90	53	212.0	76.74	36.2	34.7

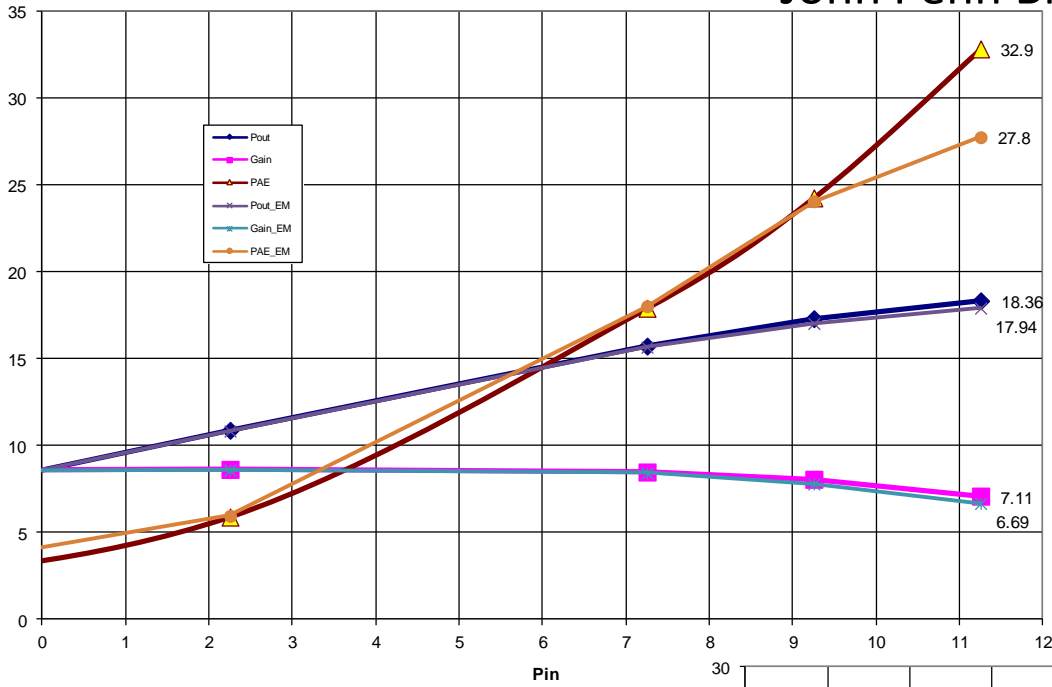
John Penn BroadBand Amplifiers (1-5 GHz)

4 GHz	Die#1	1-5 GHz Fall12 TQP13			4V ; 53 mA				
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE
-10.0	1.43	-11.35	2.78	14.13	53	212.0	1.90	0.9	0.9
-5.0	6.54	-6.35	7.89	14.24	53	212.0	6.15	2.9	2.8
-2.0	9.55	-3.35	10.90	14.25	53	212.0	12.30	5.8	5.6
0.0	11.59	-1.35	12.94	14.29	53	212.0	19.68	9.3	8.9
2.0	13.46	0.65	14.81	14.16	53	212.0	30.27	14.3	13.7
4.0	15.07	2.65	16.42	13.77	53	212.0	43.85	20.7	19.8
5.0	15.77	3.65	17.12	13.47	53	212.0	51.52	24.3	23.2
6.0	16.35	4.65	17.70	13.05	53	212.0	58.88	27.8	26.4
7.0	16.82	5.65	18.17	12.52	53	212.0	65.61	31.0	29.2
2.0	14.14	0.65	15.49	14.84	53	212.0	35.40	16.7	16.2
4.0	15.88	2.65	17.23	14.58	53	212.0	52.84	24.9	24.1
5.0	16.57	3.65	17.92	14.27	53	212.0	61.94	29.2	28.1
6.0	17.15	4.65	18.50	13.85	53	212.0	70.79	33.4	32.0
7.0	17.62	5.65	18.97	13.32	53	212.0	78.89	37.2	35.5

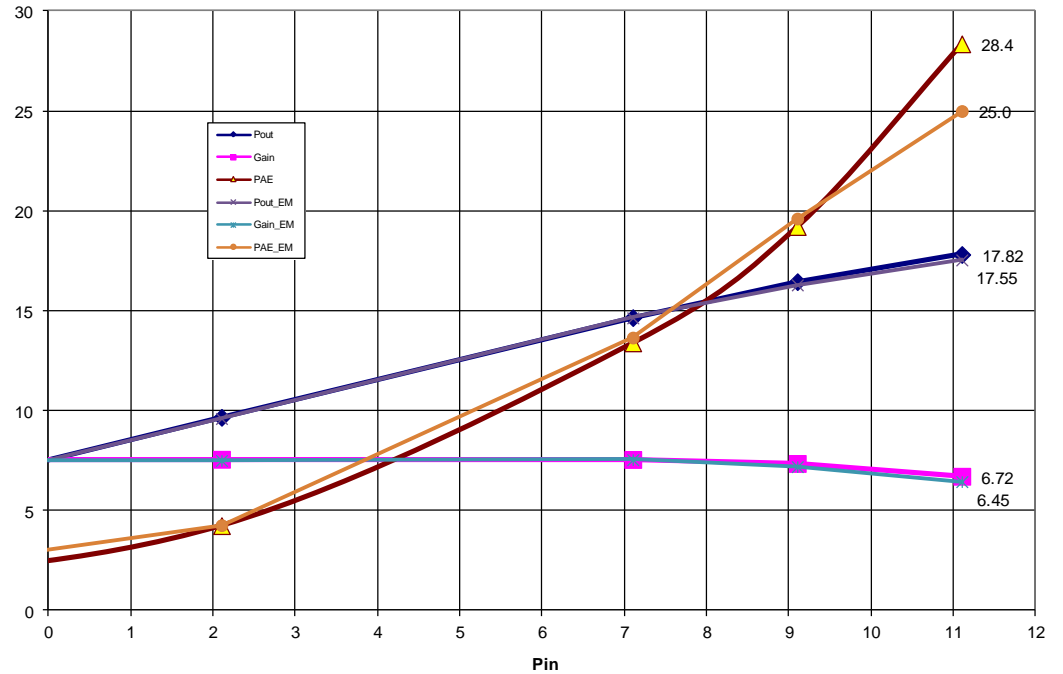
5 GHz	Die#1	1-5 GHz Fall12 TQP13			4V ; 53 mA				
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE
-10.0	0.01	-11.60	1.61	13.21	53	212.0	1.45	0.7	0.7
-5.0	5.11	-6.60	6.71	13.31	53	212.0	4.69	2.2	2.1
-2.0	8.16	-3.60	9.76	13.36	53	212.0	9.46	4.5	4.3
0.0	10.16	-1.60	11.76	13.36	53	212.0	15.00	7.1	6.7
2.0	12.08	0.40	13.68	13.28	53	212.0	23.33	11.0	10.5
4.0	13.98	2.40	15.58	13.18	53	212.0	36.14	17.0	16.2
5.0	14.73	3.40	16.33	12.93	53	212.0	42.95	20.3	19.2
6.0	15.32	4.40	16.92	12.52	53	212.0	49.20	23.2	21.9
7.0	15.89	5.40	17.49	12.09	53	212.0	56.10	26.5	24.8
8.0	16.38	6.40	17.98	11.58	53	212.0	62.81	29.6	27.6
2.0	12.46	0.40	14.06	13.66	53	212.0	25.47	12.0	11.5
4.0	14.22	2.40	15.82	13.42	53	212.0	38.19	18.0	17.2
5.0	14.97	3.40	16.57	13.17	53	212.0	45.39	21.4	20.4
6.0	15.56	4.40	17.16	12.76	53	212.0	52.00	24.5	23.2
7.0	16.13	5.40	17.73	12.33	53	212.0	59.29	28.0	26.3
8.0	16.62	6.40	18.22	11.82	53	212.0	66.37	31.3	29.2

PA 11-19GHz 14GHz EM Meas 12
4V ~44mA

John Penn BroadBand Amplifiers (11-19 GHz)



PA 11-19GHz 16GHz EM Meas 12
4V ~44mA



John Penn BroadBand Amplifiers (11-19 GHz)

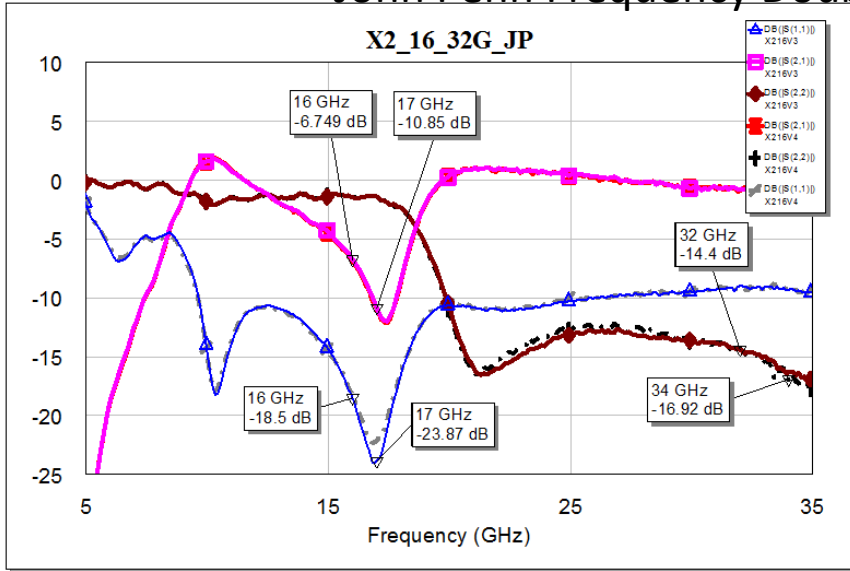
12 GHz	Die#1	11-19 GHz Fall12 TQP13				4V ; 45 mA				
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE	
-5.0	-1.32	-7.40	1.08	8.48	45	180.0	1.28	0.7	0.6	
0.0	3.67	-2.40	6.07	8.47	45	180.0	4.05	2.2	1.9	
5.0	8.71	2.60	11.11	8.51	45	180.0	12.91	7.2	6.2	
10.0	13.35	7.60	15.75	8.15	45	180.0	37.58	20.9	17.7	
12.0	14.66	9.60	17.06	7.46	47	188.0	50.82	27.0	22.2	
14.0	15.43	11.60	17.83	6.23	42	168.0	60.67	36.1	27.5	

14 GHz	Die#1	11-19 GHz Fall12 TQP13				4V ; 45 mA				
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE	
-5.0	-1.89	-7.75	0.86	8.61	45	180.0	1.22	0.7	0.6	
0.0	3.09	-2.75	5.84	8.59	45	180.0	3.84	2.1	1.8	
5.0	8.15	2.25	10.90	8.65	45	180.0	12.30	6.8	5.9	
10.0	13.00	7.25	15.75	8.50	45	180.0	37.58	20.9	17.9	
12.0	14.58	9.25	17.33	8.08	47	188.0	54.08	28.8	24.3	
14.0	15.61	11.25	18.36	7.11	42	168.0	68.55	40.8	32.9	

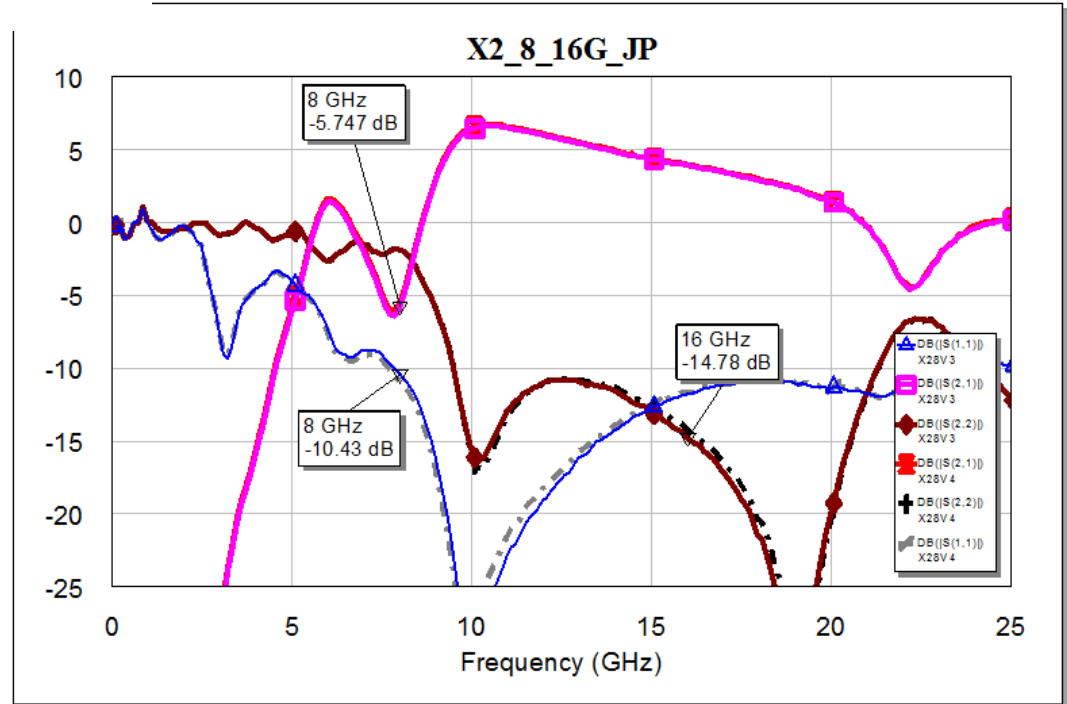
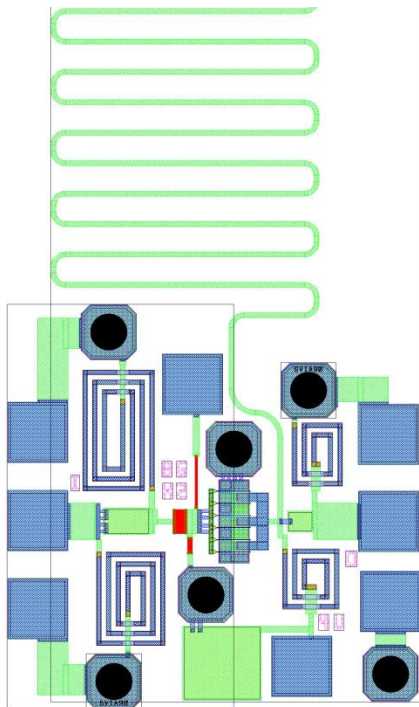
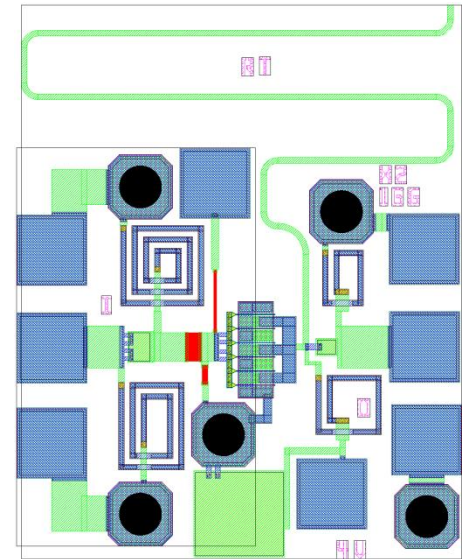
16 GHz	Die#1	11-19 GHz Fall12 TQP13				4V ; 45 mA				
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE	
-5.0	-3.23	-7.90	-0.33	7.57	45	180.0	0.93	0.5	0.4	
0.0	1.73	-2.90	4.63	7.53	45	180.0	2.90	1.6	1.3	
5.0	6.77	2.10	9.67	7.57	45	180.0	9.27	5.1	4.2	
10.0	11.76	7.10	14.66	7.56	45	180.0	29.24	16.2	13.4	
12.0	13.56	9.10	16.46	7.36	47	188.0	44.26	23.5	19.2	
14.0	14.92	11.10	17.82	6.72	42	168.0	60.53	36.0	28.4	

14 GHz	Die#1	11-19 GHz EM Fall12 TQP13				4V ; 44 mA				
Pin(SG)	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE	
-5.0	-1.92	-7.75	0.83	8.58	44	176.0	1.21	0.7	0.6	
0.0	3.08	-2.75	5.83	8.58	44	176.0	3.83	2.2	1.9	
5.0	8.11	2.25	10.86	8.61	44	176.0	12.19	6.9	6.0	
10.0	12.94	7.25	15.69	8.44	44	176.0	37.07	21.1	18.0	
12.0	14.31	9.25	17.06	7.81	44	176.0	50.82	28.9	24.1	
14.0	15.19	11.25	17.94	6.69	44	176.0	62.23	35.4	27.8	

John Penn Frequency Doublers (8 to 16 GHz, 16 to 32 GHz)



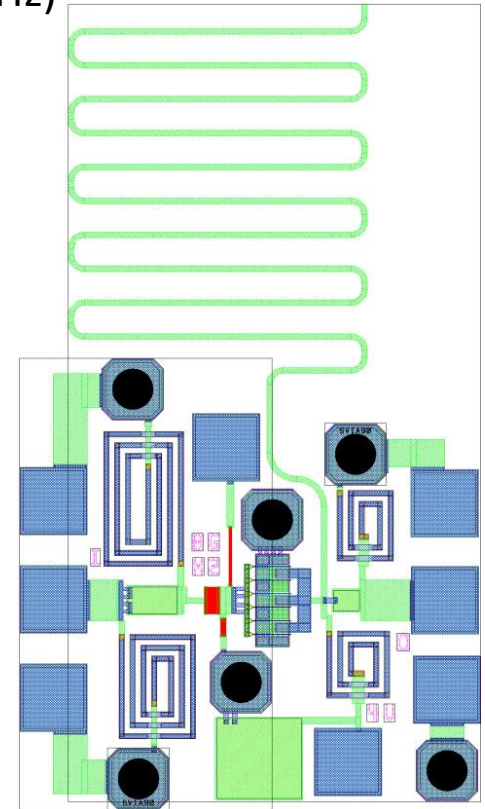
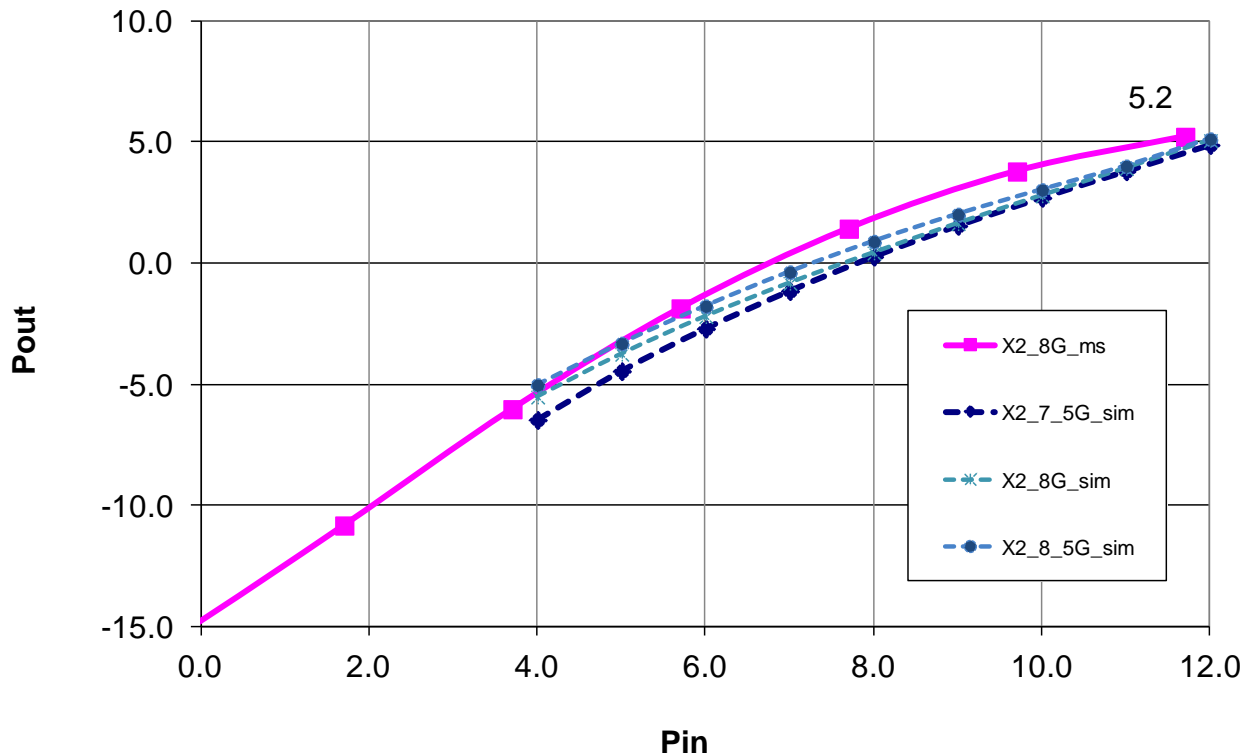
These 2012 designs “re-tune” the harmonic stub from the 2011 designs. An article was in High Frequency Magazine in Feb 2013. The “EM” simulation of the stub was close to the measured peak attenuation.



John Penn Frequency Doublers (8 to 16 GHz, 16 to 32 GHz)

Doublers 8G		4V at 39mA, vg=-1.5v			Die #1	7.8GHz		
SG	Pin(corr)	Pout8G(m	Pout16G(ms	Pout24G(ms	Pout(corr)	Pout2X(corr)	Pout3X(corr)	Cnvloss
-4.0	-6.3	-14.3	-30.9		-12.3	-27.9		21.6
-2.0	-4.3	-12.4	-27.0		-10.4	-24.0		19.7
0.0	-2.3	-10.4	-22.7		-8.4	-19.7		17.4
2.0	-0.3	-8.5	-18.4		-6.5	-15.4		15.1
4.0	1.7	-6.6	-13.8	-33.2	-4.6	-10.8	-28.7	12.5
6.0	3.7	-4.9	-9.0	-24.8	-2.9	-6.0	-20.3	9.7
8.0	5.7	-3.4	-4.8	-18.7	-1.4	-1.8	-14.2	7.5
10.0	7.7	-1.9	-1.6	-14.3	0.2	1.5	-9.8	6.3
12.0	9.7	-0.5	0.8	-10.2	1.5	3.8	-5.7	5.9
14.0	11.7	0.6	2.2	-6.8	2.6	5.2	-2.3	6.5

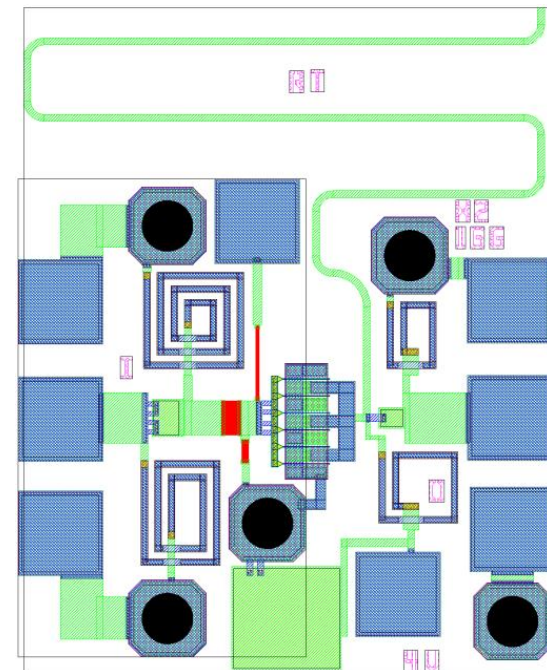
X2 8 GHz P2X vs. P1In Meas/Sim 4/15/13



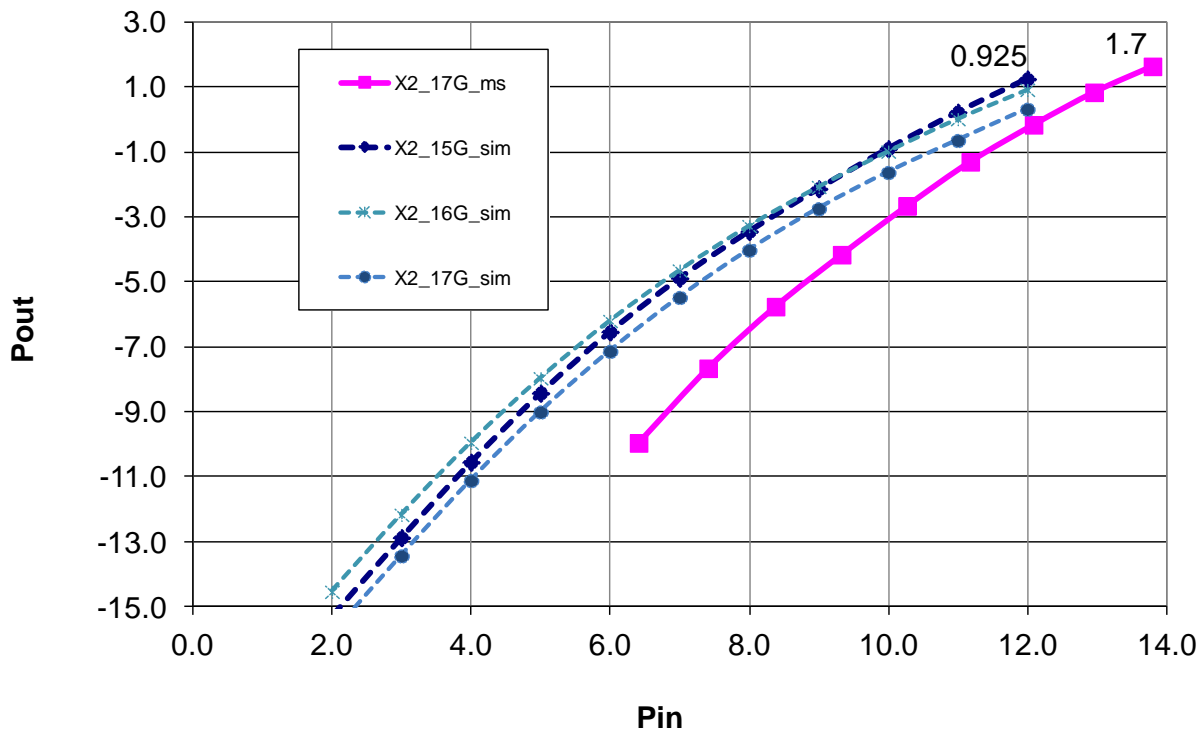
The 8 GHz doubler performance closely matched the original simulation for the design. ~6dB conversion loss (X2)

John Penn Frequency Doublers (8 to 16 GHz, 16 to 32 GHz)

5/21/2013		17.0 GHz							
Doubler 16G		4V at ~34mA, vg=-3v		Die #2					
Pin(SG)	Pin(A)	PoutX1(m)	PoutX2(r)	Pout(corr)	Pout2X(cc)	Convloss	dBc	I(4V)	
-8.00	6.4	-8.08	-17.00	-2.4	-10.0	16.4	7.6	40.3	
-7.00	7.4	-7.11	-14.70	-1.4	-7.7	15.1	6.3	43.8	
-6.00	8.4	-6.22	-12.80	-0.5	-5.8	14.1	5.2	47.7	
-5.00	9.3	-5.32	-11.20	0.4	-4.2	13.5	4.5	52.2	
-4.00	10.3	-4.44	-9.70	1.3	-2.7	12.9	3.9	57.0	
-3.00	11.2	-3.60	-8.34	2.1	-1.3	12.5	3.4	62.2	
-2.00	12.1	-2.81	-7.20	2.9	-0.2	12.2	3.1	67.5	
-1.00	13.0	-2.07	-6.20	3.6	0.9	12.1	2.8	72.8	
0.00	13.8	-1.42	-5.40	4.3	1.7	12.2	2.6	77.8	

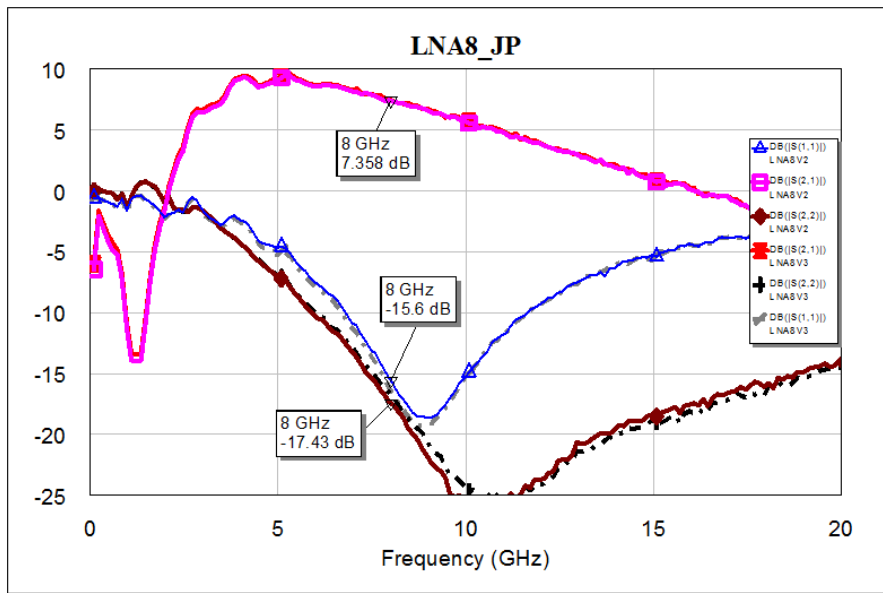
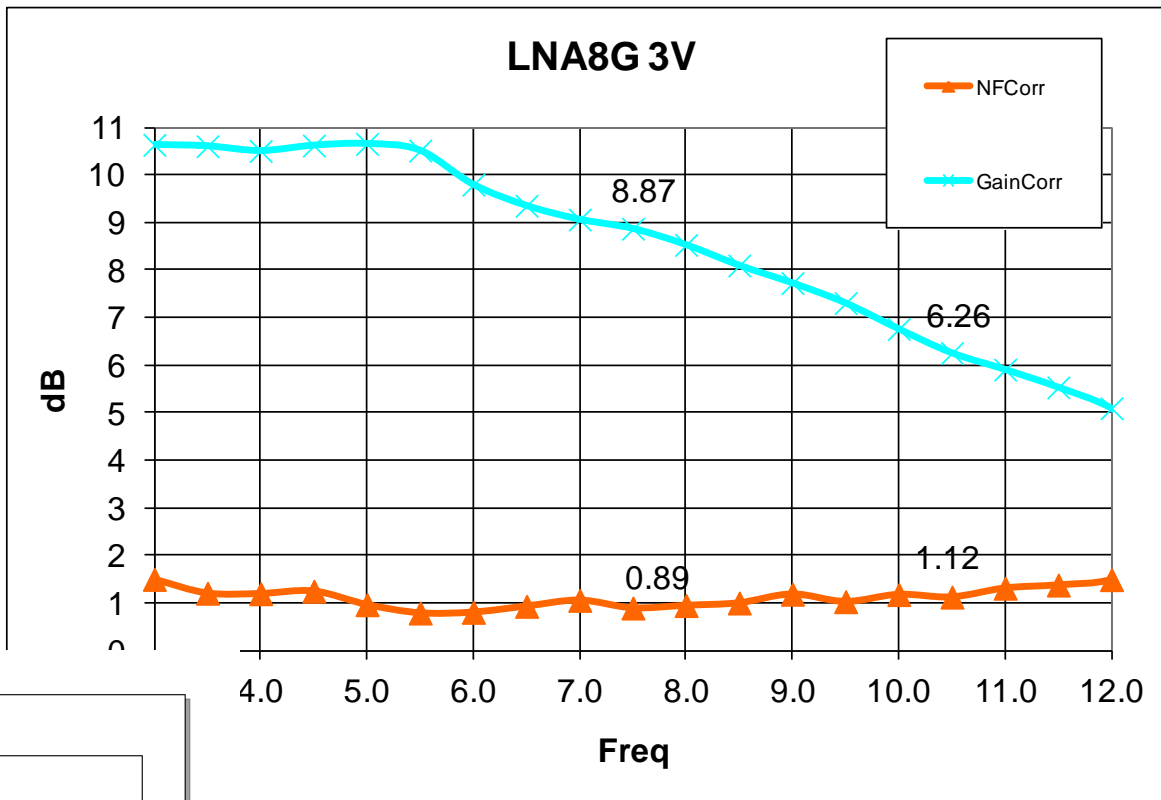
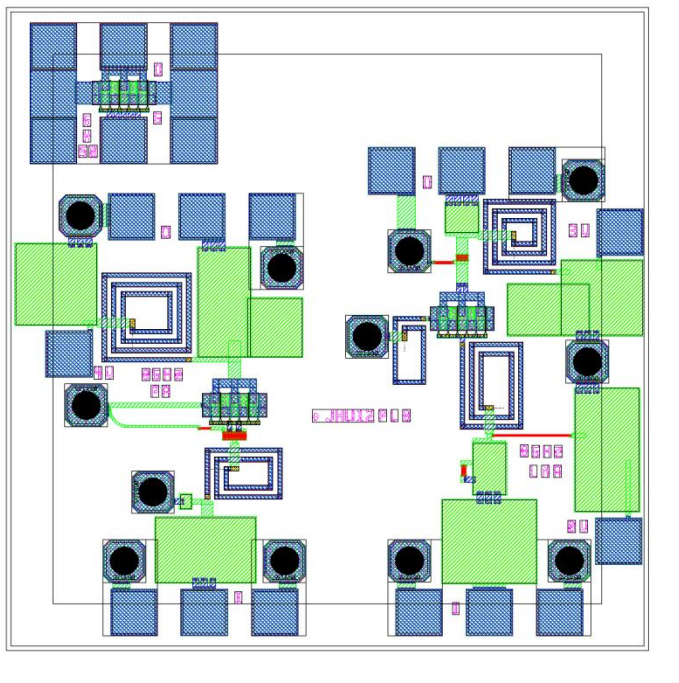


X2 17 GHz P2X vs. P1In Meas/Sim 5/21/13



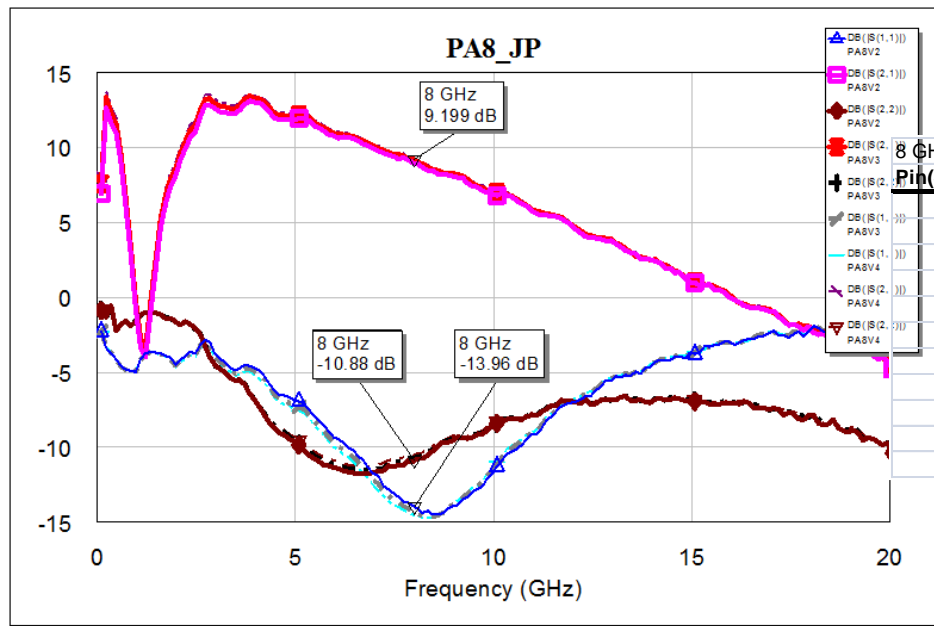
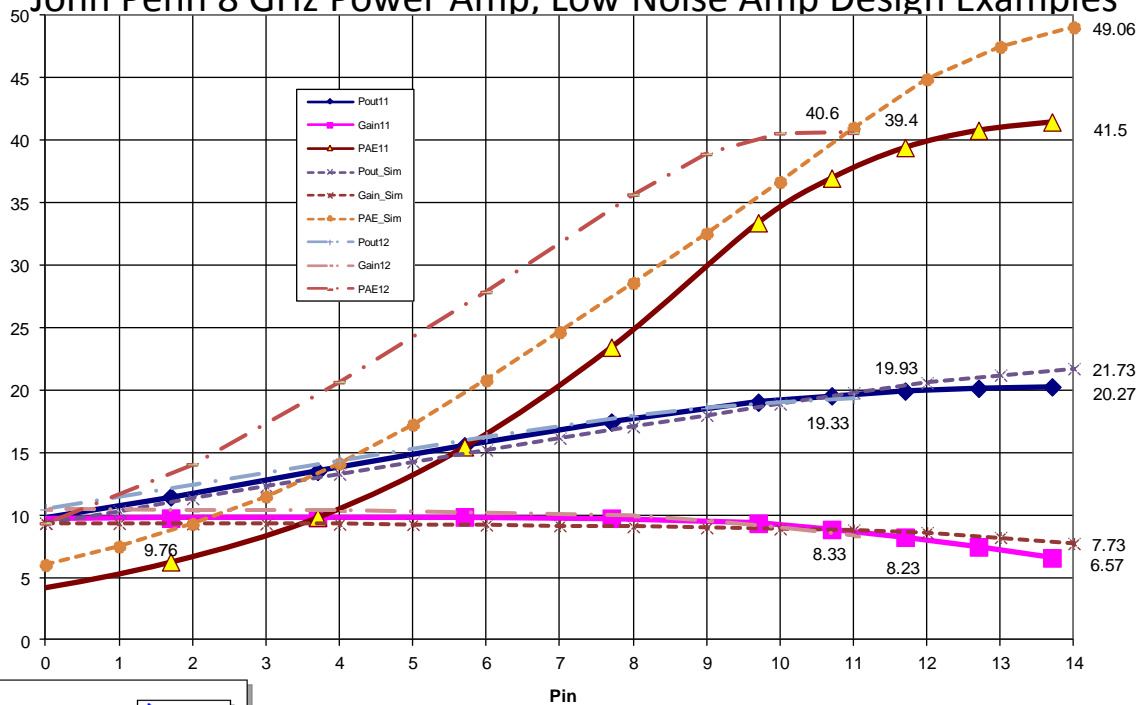
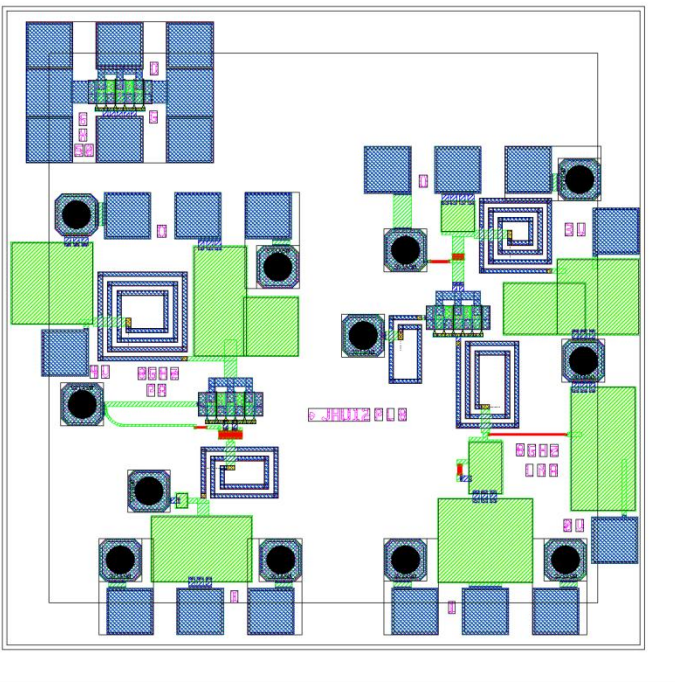
The 16 GHz doubler performance closely matched the original simulation for the design. ~12dB conversion loss (X2)

John Penn 8 GHz Power Amp, Low Noise Amp Design Examples



Class Amp Examples: Same as 2011 Fab
 Low Noise Amp 8 GHz
 LN8V2 2V 16 mA vgs=0V --Die #1
 LN8V3 3V 20 mA vgs=0V --Die #1
 Power Amp 8 GHz
 PA8V2 2V 17 mA vgs=0V --Die #1
 PA8V3 3V 23 mA vgs=0V --Die #1
 PA8V4 4V 29 mA vgs=0V --Die #1

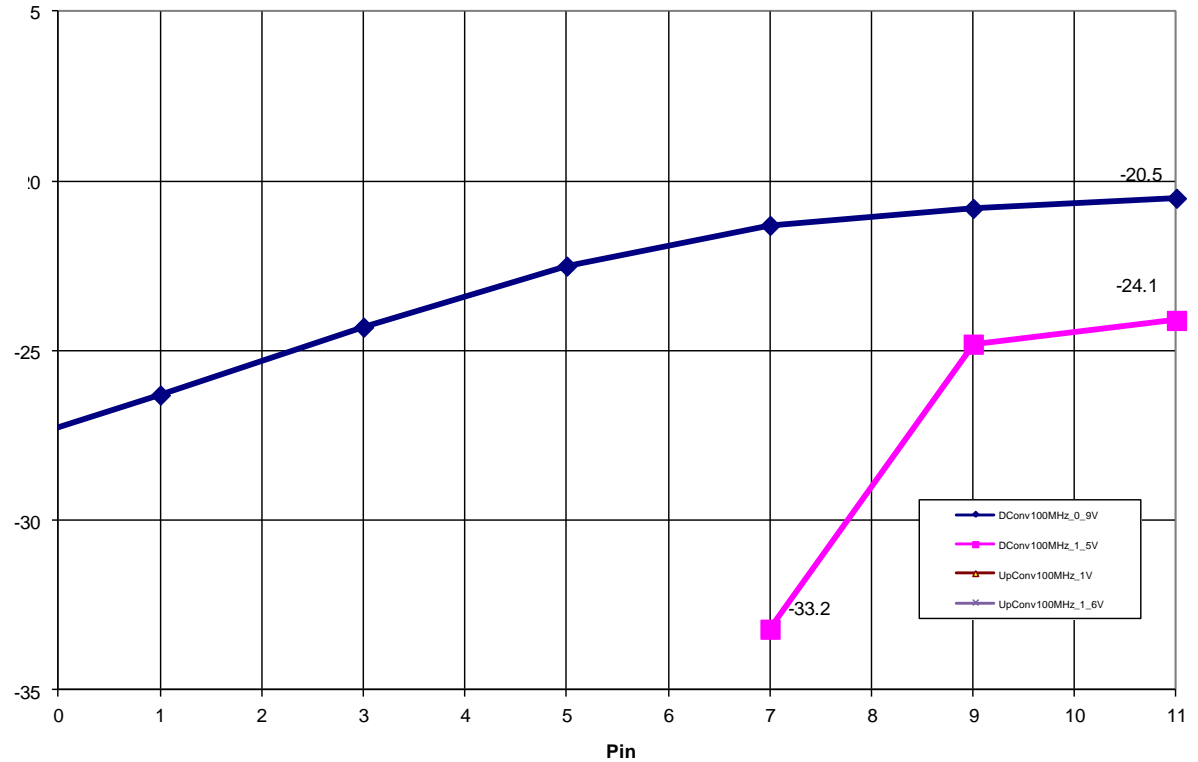
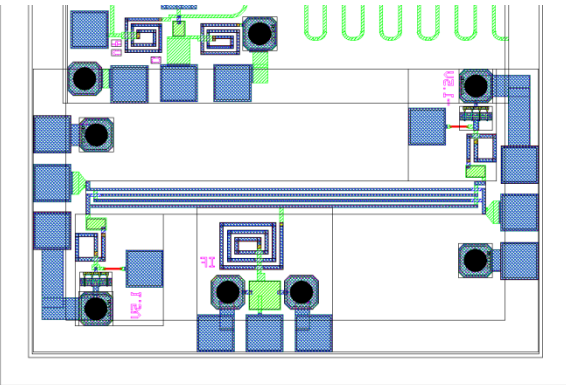
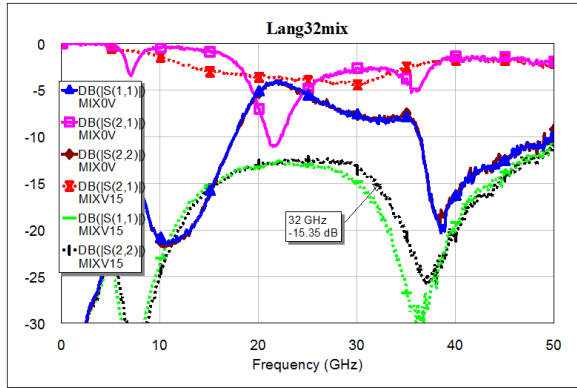
PA 8GHz Meas vs Sim 11 & 12 4V John Penn 8 GHz Power Amp, Low Noise Amp Design Examples



8 GHz		8 GHz Fall12 TQP13				4V ; 27 mA				
Pin(SG)	Die#1	Pout(SA)	Pin(corr)	Pout(corr)	Gain	I1(4V)	PDC(mw)	Pout(mw)	Drn Eff	PAE
-10.0	-3.56	-12.00	-1.56	10.44	27	108.0	0.70	0.6	0.6	0.6
-5.0	1.45	-7.00	3.45	10.45	27	108.0	2.21	2.0	1.9	1.9
0.0	6.46	-2.00	8.46	10.46	27	108.0	7.01	6.5	5.9	5.9
2.0	8.45	0.00	10.45	10.45	27	108.0	11.09	10.3	9.3	9.3
4.0	10.39	2.00	12.39	10.39	28	112.0	17.34	15.5	14.1	14.1
6.0	12.36	4.00	14.36	10.36	30	120.0	27.29	22.7	20.6	20.6
8.0	14.22	6.00	16.22	10.22	34	136.0	41.88	30.8	27.9	27.9
10.0	15.92	8.00	17.92	9.92	39	156.0	61.94	39.7	35.7	35.7
11.0	16.56	9.00	18.56	9.56	41	164.0	71.78	43.8	38.9	38.9
12.0	17.02	10.00	19.02	9.02	43	172.0	79.80	46.4	40.6	40.6
13.0	17.33	11.00	19.33	8.33	45	180.0	85.70	47.6	40.6	40.6

John Penn Diode Mixer

JP Meas 12
Mixer Down Conversion

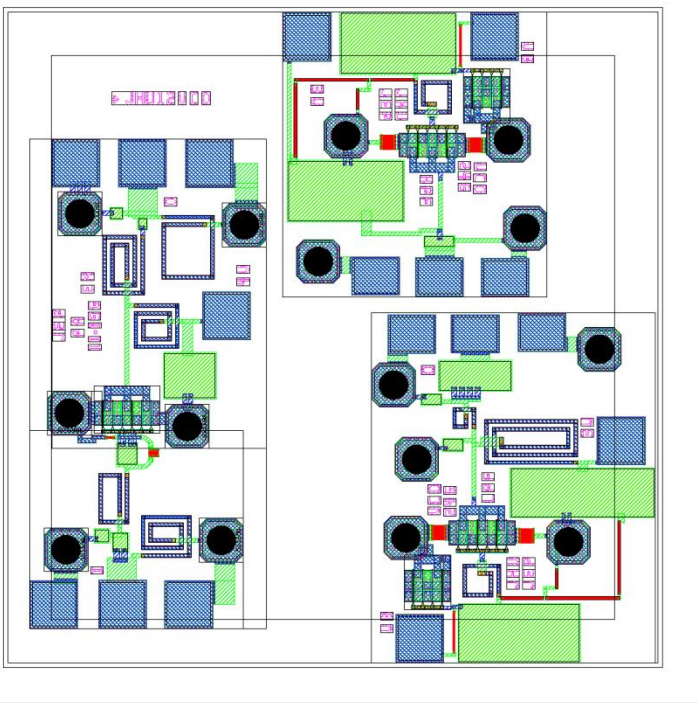


4/25/2013				RF25.2 GHz and IF 800 MHz -5 dBm se			
LO = 26 GHz				~5dB loss to LO			
1) RF 25.2 GHz				~1 dB loss to IF			
Down Conversion		IF=800 MHz		Vb=+/-1.5V		IF=100 MHz Vb=0V	
LO 26G	LO (corr)	IF (meas)	RF (corr)	Loss (gain)	IF (meas)	Loss (gain)	
0	-5	-47.5	-14.5	-32.0			
6	1	-41.8	-14.5	-26.3			
8	3	-39.8	-14.5	-24.3			
10	5	-38.0	-14.5	-22.5			
12	7	-36.8	-14.5	-21.3	-48.7	-33.2	
14	9	-36.3	-14.5	-20.8	-40.3	-24.8	
16	11	-36.0	-14.5	-20.5	-39.6	-24.1	

Diode Mixer using a Lange Coupler
Works best with 1.5 V forward bias on the diodes. Still works OK at high LO drive w/o bias.
Simple LC IF Filter.

John Penn Voltage Controlled Oscillators (24 GHz)

The 2011 Class had 10 and 20 GHz VCO designs. These 24 GHz VCO designs are similar with a re-tuning of the previous design. The High Pass output match tends to be more robust in oscillation but has higher harmonics than the Low Pass output match. Die has LP/HP 24 GHz VCOs and a broadband 11-20 GHz amplifier.



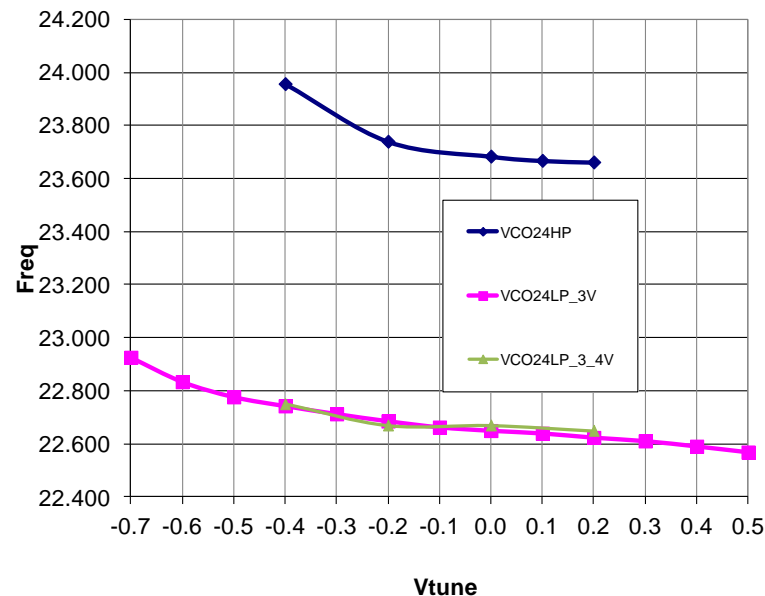
Measured MWO VCO 24 GHz HPF

John Penn
4/15/2013

LPF VCO	3V at 20mA	Die #1
VBias (V)	Freq (GHz Pout(ms))	Pout(corr)
-0.7	22.925	-4.4
-0.6	22.833	-6.1
-0.5	22.776	-7.0
-0.4	22.742	-7.1
-0.3	22.712	-6.8
-0.2	22.685	-8.2
-0.1	22.662	-8.5
0.0	22.649	-8.8
0.1	22.639	-8.9
0.2	22.623	-9.0
0.3	22.610	-9.1
0.4	22.59	-8.8
0.5	22.568	-9.8

HPF VCO	3V at 24mA	Die #1
VBias (V)	Freq (GHz Pout(ms))	Pout(corr)
-0.4	23.956	2.7
-0.2	23.739	3.6
0.0	23.683	3.5
0.1	23.667	3.2
0.2	23.661	3.0

VCO Freq vs. Tune Voltage



John Penn Test Circuits, Cal Structures, etc.

Various Cal structures,
800 um mlin,
PHEMTs,
Switches, etc.

